

Correct Use of Tantalum Chip Capacitors

Be sure to read this before using NEC TOKIN Tantalum Capacitors.

[Notes]

- Be sure to read "Notes on Using The Solid Tantalum Capacitor" (p34 p42) and "Cautions" (p43) before commencing circuit design or using the capacitor.
- Confirm the usage conditions and rated performance of the capacitor before use.
- Ninety percent of the failure that occurs in this capacitor is caused by an increase in leakage current or short-circuiting. It is therefore important to make sufficient allowances for redundant wiring in the circuit design.

[Quality Grades]

NEC TOKIN devices are classified into the following quality grades in accordance with their application (for details of the applications, see p43). The quality grade of all devices in this document is "standard"; the devices in this document cannot be used for "special" or "specific" quality grade applications. Customers who intend to use a product or products in this document for applications other than those specified under the "standard" quality grade must contact NEC TOKIN sales representative in advance (see the reverse side of the cover for contact details).

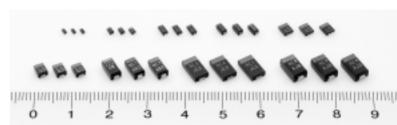
- Standard: This quality grade is intended for applications in which failure or malfunction of the device is highly unlikely to cause harm to persons or damage to property, or be the source of any negative effects or problems in the wider community.
- Special: This quality grade is intended for special applications that have common requirements, such specific industrial fields. Devices with a "special" quality grade are designed, manufactured, and tested using a more stringent quality assurance program than that used for "standard" grade devices. There is a high possibility that failure or malfunction of the device when being used for applications in this category will cause harm to persons or damage to property, or create negative effects or problems in the wider community.
- Specific: Devices with a "specific" quality grade are designed, manufactured, and tested using a quality assurance program that is designated by the customer or that is created in accordance with the customer's specifications. There is an extremely high possibility that failure or malfunction of the device when being used for applications in this category will cause harm to persons or damage to property, or create serious problems in the wider community. Customers who use NEC TOKIN's products for these "specific" applications must conclude an individual quality agreement and/or development agreement with NEC TOKIN. A quality assurance program designated by the customer must also be determined in advance.

NEC TOKIN offers the latest technology

<Tantalum Capacitors>

<Conductive Polymer Tantalum Capacitors>
"NeoCapacitors"





NEC has been manufacturing solid electrolyte tantalum capacitors for more than 30 years. As a result of NEC's active research and development programs, NEC capacitors offer the designer the latest technology plus outstanding performance. NEC capacitors are used extensively in industrial, commercial, entertainment, and medical electronic equipment.

NEC has obtained ISO 9001 and QS9000 certificates of registration for capacitors.

NEC, in response to the wave of the worldwide environment protection consciousness, developed E/SV series by eliminating lead from the terminals. The low-ESR conductive polymer tantalum capacitors are expected to meet an important market need; they are suited for DC/DC converters, video cameras, personal handy phones, etc.

The business of manufacturing and sale of capacitors was divided and transferred to Tokin, as of April 1, 2002. Then Tokin changed its corporate name to "NEC TOKIN Corporation," which has charge of electronic components business within the NEC Group.

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TANTALUM CAPACITORS

Description

NEC TOKIN's tantulum capacitors offer the designer advanced technological design and excellent performance characteristics for filtering, bypassing, coupling, decoupling, blocking, and R C timing circuits. They are used extensively in industrial, commercial, entertainment, and medical electronic equipment.

The tantalum capacitor is inherently very reliable and there is significant evidence that this reliability improves with age-perhaps indefinitely. Capacitance loss with age and other problems often associated with liquid electrolytes are nonexistent in solid electrolyte tantalums.

A process used to further improve the reliability of tantalums is to burn them in at elevated voltages at 85°C for extended periods of time, thus eliminating high leakage and other undesirable characteristics. This process is done because solid electrolyte tantalum capacitors do not conform to the exponential distribution of time ordered failures, but instead exhibit a constantly decreasing failure rate.

If you specify NEC TOKIN tantalums, you can feel confident that you are getting the best available quality, reliability, and price.

TANTALUM CHIP CAPACITORS

		С	onventional Ty	pe (Manganese	Dioxide Type)	Lead-free/	Conform to RoHS
Series	Operating Temperature Range (°C)	DC Rated Voltage Range (V)	Capacitance Range (µF)	Capacitance Tolerance (%)	DC Leakage Current (μA)	Dissipation Factor (%)	Features
E/SV	−55 to +125	2.5 to 35	0.47 to 680	±20 or ±10 (P, J case;±20)	0.01 CV ⁽¹⁾ or 0.5 whichever is greater	2.5 Vdc to 10 Vdc ⁽²⁾ : 8 to 30 16 Vdc to 35 Vdc : 4 to 15	Standard Miniaturized Ultra miniaturized
F/SV	-55 to +125	2.5 to 4	33 to 47	±20	0.01 CV ⁽¹⁾ or 0.5 whichever is greater	30	Face down terminal Ultra miniaturized Large Capacitance
SV/Z	-55 to +125	4 to 35	6.8 to 330	±20 or ±10	0.01 CV ⁽¹⁾ or 0.5 whichever is greater	6 to 14 ⁽³⁾	Low ESR
			NeoCapacitor	(Conductive Po	lymer Type)	Lead-free/	Conform to RoHS
PS/L	-55 to +105	2.5 to 16	2.2 to 1000	±20	0.1 CV ⁽¹⁾ or 3, (J case:10) whichever is greater	4 to 10 ⁽⁴⁾	Ultra-low ESR
PS/G	-55 to +105	2.5	330 to 680	±20	0.1 CV ⁽¹⁾ or 3, whichever is greater	10	Ultra-low ESR (Single digit ESR)

Notes 1. Product of capacitance in μ F and voltage in V.

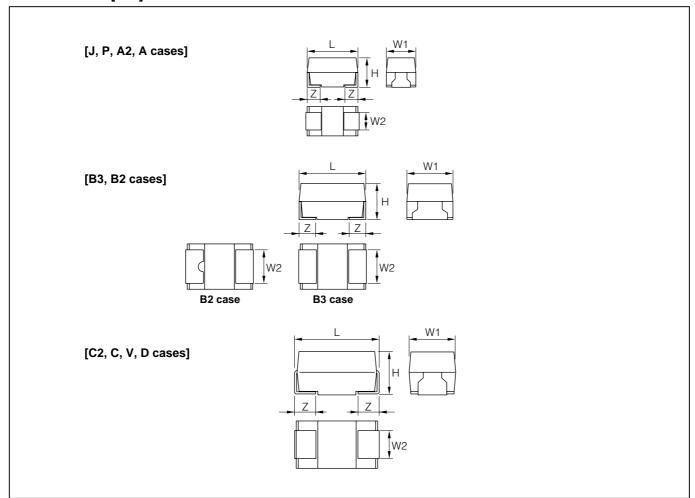
- 2. Refer to Standard Ratings on page 9, 10, 11. 3. Refer to Standard Ratings on page 16.
- 4. Refer to Standard Ratings on pages 25, 26.

E/SV Series Tantalum Chip Capacitors

■ FEATURES

- Lead-free Type. In conformity to RoHS.
- Offer a range of small, high-capacity models.
- Succeed to the latest technology plus outstanding peformance.

■ DIMENSIONS [mm]



(Unit: mm)

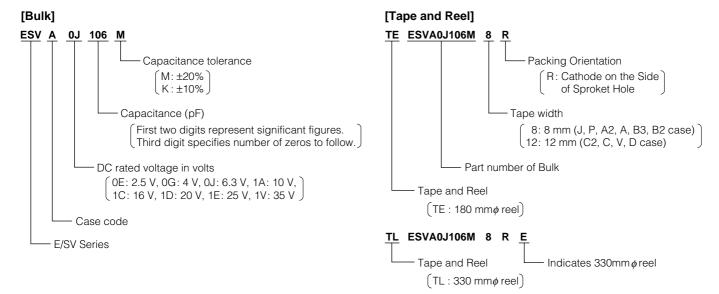
Case Code	EIA code	L	W 1	W ₂	н	z
J	_	1.6 ± 0.1	0.8 ± 0.1	0.6 ± 0.1	0.8 ± 0.1	0.3 ± 0.15
Р	2012	2.0 ± 0.2	1.25 ± 0.2	0.9 ± 0.1	1.1 ± 0.1	0.5 ± 0.1
A2 (U)	3216L	3.2 ± 0.2	1.6 ± 0.2	1.2 ± 0.1	1.1 ± 0.1	0.8 ± 0.2
Α	3216	3.2 ± 0.2	1.6 ± 0.2	1.2 ± 0.1	1.6 ± 0.2	0.8 ± 0.2
B3 (W)	3528L	3.5 ± 0.2	2.8 ± 0.2	2.2 ± 0.1	1.1 ± 0.1	0.8 ± 0.2
B2 (S)	3528	3.5 ± 0.2	2.8 ± 0.2	2.2 ± 0.1	1.9 ± 0.2	0.8 ± 0.2
C2	_	6.0 ± 0.2	3.2 ± 0.2	2.2 ± 0.1	1.4 ± 0.1	1.3 ± 0.2
С	6032	6.0 ± 0.2	3.2 ± 0.2	2.2 ± 0.1	2.5 ± 0.2	1.3 ± 0.2
V	_	7.3 ± 0.2	4.3 ± 0.2	2.4 ± 0.1	1.9 ± 0.1	1.3 ± 0.2
D	7343	7.3 ± 0.2	4.3 ± 0.2	2.4 ± 0.1	2.8 ± 0.2	1.3 ± 0.2

■ STANDARD C-V VALUE REFERENCE BY CASE CODE

	UR	2.5V	4V	6.3V	10V	16V	20V	25V	35V
μ F		0E	0G	0J	1A	1C	1D	1E	1V
0.47	474					P	A2	A	A
0.68	684					P	A2	A	A
1.0	105				P	J, P	A2	P, A2, A	A2, A
1.5	155			P	J, P	A	A2		A
2.2	225			J	J, P	P, A2, A, [J]	P, A2, A	A, [P]	A, B2
3.3	335		P	J	P, A2	A2, A	A, B3	A	B2, [B3]
4.7	475			J, P, A	J, P, A2, A	A2, A	A2, A, B3, B2	B3, B2, [A2]	С
6.8	685		J	J, P, A2	A2, A	A, B3	B2		С
10	106	J	J, P	J, P, A2, A	P, A2, A, B2	A, B3, B2	B2	C, [B2]	C, D
15	156		P	P, A2, A	B3, [P]	B2, [A]	С	C	D
22	226	P, A2	P, A2, A	P, A2, A, B3, B2	A, B3, B2, [A2]	B3, B2, C	C2, C, D	D	
33	336	P, A2	P, A2, A	A, B3, [A2]	B3, B2, [A]	C2, C, [B2]	D	D	
47	476	P, A2, A	P, A2, A, B3	A, B3, B2, C	B2, C2, C, [B3]	C, D	D	[D]	
68	686	A	A, B3	B2, C2	B2, C2, C	C, D			
100	107	B3, B2	A, B3, B2, C2	B2, C2, C, [B3]	C, V, D, [C2]	D			
150	157	A, B3, C2	B2, C2	С	V, D				
220	227	B2, C2	B2, C	C, V, D	D				
330	337	B2, C	C, V	D					
470	477	C, D	D	D					
680	687		D						

^{[]:}Under development

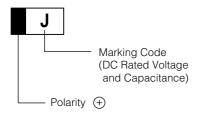
■ PART NUMBER SYSTEM



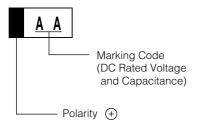
■ MARKINGS

The standard marking shows capacitance, DC rated voltage, and polarity.

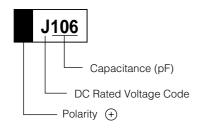
[J case] (ex. $4.7 \mu F / 6.3 V$)



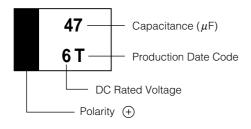
[P case] (ex. 1 μ F / 10 V)



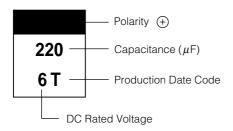
[A2, A cases] (ex. $10 \,\mu\text{F} / 6.3 \,\text{V})$



[B3, B2 cases] (ex. $47 \,\mu\text{F} / 6.3 \,\text{V})$



[C2, C, V, D cases] (ex. $220 \,\mu\text{F} / 6.3 \,\text{V})$



[J case Marking Code]

U _R μ F	2.5 V	4 V	6.3 V	10 V	16 V
1.0					၁
1.5				A	
2.2			ſ	4	
3.3			7		
4.7			J	≻	
6.8		G	ے		
10	е	G	r		

[P case Marking Code]

UR μ F	2.5 V	4 V	6.3 V	10 V	16 V	20V	25V
0.47					CS		
0.68					CW		
1				AA	CA		EA
1.5			JE	AE			
2.2				AJ	CJ	DJ	
3.3		GN		AN			
4.7			JS	AS			
6.8			JW				
10		GĀ	JĀ	ΑĀ			
15		GĒ	JĒ				
22	еJ	GJ	JJ				
33	еÑ	GÑ					
47	eS	GŜ					

[P, A2, A, cases DC Rated Voltage code]

Code	е	G	J	Α	С	D	E	٧
Rated Voltage	2.5 V	4 V	6.3 V	10 V	16 V	20 V	25 V	35V

[B3, B2, C2, C, V, D cases Production date code]

YM	Jan.	Feb.	Mar.	Apr.	May	Jun.	Jul.	Aug.	Sep.	Oct.	Nov.	Dec.
2003	а	b	С	d	е	f	g	h	j	k	- 1	m
2004	n	р	q	r	S	t	u	٧	w	х	у	z
2005	Α	В	С	D	Е	F	G	Н	J	K	L	М
2006	N	Р	Q	R	S	Т	U	V	W	Χ	Υ	Z

Note: Production date code will repeat beginning in 2007.

■ PERFORMANCE CHARACTERISTICS

Test Conditions	: Conform to	IFC 60384-1

ITEM					PERI	FOR	MANCE				TEST CONDITION
Operating tempera	ture				-55°	C to +	+125°C				Derate voltage at 85°C at more
Rated voltage (V.d	lc)	2.5V	4V	6.3\	/ 10\	V	16V	20V	25V	35V	at 85°C
Derated voltage (V	'.dc)	1.6V	2.5V	4V	6.3	V	10V	13V	16V	22V	at 125°C
Surge voltage (V.d	lc)	3.3V	5.2V	8V	13\	V	20V	26V	33V	46V	at 85°C
Capacitance					0.47 ֈ	μF to	680 μF		•		
Capacitance tolera	ince			±2	20% or ±10	0% (P	,J case: ±	20%)			at 120 Hz
DC Leakage Curre	ent (L.C)		0	.01C • \	V(μA) or 0.	.5 μΑ	, whicheve	r is great	er		Voltage: Rated voltage for 5min.
Dissipation Factor					Refer to	Stand	lard Rating	ıs			at 120 Hz
Equivalent Series I	Resistance				Refer to	Stand	lard Rating	ıs			at 100 kHz
		Capac	itance char	nge		DF(%	%)		L.C		
Surge voltage test		Refer to S	Standard R	atings		er tha	ın initial ation		Lower than specifica		Temperature : 85±2°C Applied voltage : Surge voltage Series resistance : 33 ohm Duration of surge : 30±5 sec Time between surge : 5.5min. Number of cycle : 1000
	-55°C	Not to exceed or -12%	ed -20% (P,	Refer to	Stand	dard Rating	ıs		_	Step 1: 25±2°C	
Characteristic at high and low temperature	+85°C	Not to exceed +20% (P, J case) or +12%				er tha	n initial ation		.1C•V(μA) nich ever is		Step 2: -55.3°C Step 3: 25±2°C
temperature	+125°C	Not to exceed +20% (P, J case) or +15%			Refer to	Stand	lard Rating		.5C•V(μA) onich ever is		Step 4: 125.3°C
Rapid change of temperature		Refer to S	Standard R	atings		ver tha	ın initial ation		Lower than specifica		Parts shall be temperature cycled over a temperature range of -55 to +125°C, five times continuously as follow. Step 1: -55.3°C, 30±3min. Step 2: room temp., 10 to 15min. Step 3: 125.3°C, 30±3min. Step 4: room temp, 10 to 15min.
Resistance to Sold heat	lering	Refer to	Standard R	atings	l	er tha	ın initial ation		Lower than specifica		solder dip : 260°C, 5sec solder reflow : 260°C,10sec
Damp heat		Refer to	Standard R	atings		an 1.5 pecific	times initi	al	Lower than specifica		at 40°C at 90 to 95% RH 500 hour
Endurance		Refer to	Standard R	atings		er tha	n initial ation	specif	wer than 2 ti ication (P, J nes initial sp	case) or 1.25	at 85°C: Rated voltage at 125°C: Derated voltage 2000 hour
Failure Rate					λο=19	% / 10	000 hour				at 85°C: Rated voltage at 125°C: Derated voltage 2000 hour
Terminal Strength			Vis The		l be no evi	idence	e of mecha	nical dan	nage		Strength: 4.9N Time: 10±0.5sec. (two directions)

Reference : Derated voltage (85 to 125°C)

$$[U_T] = [U_R] - \frac{[U_R] - [U_C]}{40} (T-85)$$

 $\left[U_{T}\right] :$ Derated voltage at operating temperature

 $[U_R]: Rated\ voltage$

[Uc] : Derated voltage at 125°C T : Ambient temperature

■ STANDARD RATINGS

Rated			Part	Leakage			DF	(%)	Capaci	tance
Voltage (V)	Capacitance (μF)	Case Code	Number (Bulk)	Current (μA)	DF (%)	ESR (Ω)	–55°C	+125°C	Change 1	Change 2
	10	J	ESVJ0E106M	0.5	20	6.5	30	30	±20%	±20%
	22	P	ESVP0E226M	0.5	20	4	30	30	±20%	±20%
	22	A2	ESVA20E226M	0.5	12	3	20	14	±12%	±12%
	33 33	A2 P	ESVA20E336M ESVP0E336M	0.8	12 20	4	22 30	14 30	±12% ±20%	±12% ±20%
	47	<u>г</u> Р	ESVP0E476M	1.1	30	6	60	40	±20%	±20%
	47	A2	ESVA20E476M	1.1	12	4.5	22	14	±12%	±12%
	47	A	ESVA0E476M	1.2	12	4.5	22	16	±12%	±12%
	68	Α	ESVA0E686M	1.7	18	4.5	34	20	±12%	±12%
2.5	100	В3	ESVB30E107M	2.5	18	1.3	34	20	±15%	±15%
2.0	100	B2	ESVB20E107M	2.5	8	1	14	10	±12%	±12%
	150	Α	ESVA0E157M	3.7	30	2	60	40	±20%	±20%
	150	B3	ESVB30E157M	3.7	20	1	40	30	±15%	±15%
	150 220	C2 B2	ESVC20E157M	3.7	12	0.8	26	18	±12%	±12%
	220	C2	ESVB20E227M ESVC20E227M	5.5 5.5	18 12	0.8	34 26	18	±12% ±12%	±12% ±12%
	330	B2	ESVB20E337M	8.2	25	0.6	50	30	±12%	±20%
	330	C	ESVC0E337M	8.2	16	0.3	34	18	±12%	±12%
	470	С	ESVC0E477M	11.7	18	1.5	34	20	±12%	±12%
	470	D	ESVD0E477M	11.7	14	0.5	18	16	±12%	±12%
	3.3	Р	ESVP0G335M	0.5	20	20	30	30	±20%	±20%
	6.8	J	ESVJ0G685M	0.5	20	7.5	30	30	±20%	±20%
	10	J	ESVJ0G106M	0.5	20	6.5	30	30	±20%	±20%
	10	P	ESVP0G106M	0.5	20	6	30	30	±20%	±20%
	15	P	ESVP0G156M	0.6	20	5	30	30	±20%	±20%
	22 22	P A2	ESVP0G226M ESVA20G226M	0.8	20 12	2.8	30 22	30 16	±20% ±12%	±20% ±12%
	22	A	ESVA20G226M	0.8	8	2.5	12	10	±12%	±12%
	33	P	ESVP0G336M	1.3	20	4	30	30	±20%	±20%
	33	A2	ESVA20G336M	1.3	8	4.5	14	10	±12%	±12%
	33	Α	ESVA0G336M	1.3	10	3	14	12	±12%	±12%
	47	Р	ESVP0G476M	1.8	30	3	60	40	±20%	±20%
	47	A2	ESVA20G476M	1.8	15	4.5	30	20	±12%	±12%
	47	A	ESVA0G476M	1.8	12	2.5	22	14	±12%	±12%
4	47	B3	ESVB30G476M	1.8	12	1.7	18	15	±15%	±15%
	68 68	A B3	ESVA0G686M ESVB30G686M	2.7 2.7	12 15	2.5 1.5	22 28	14	±12% ±15%	±12% ±15%
	100	A	ESVA0G107M	4	30	2	60	40	±20%	±20%
	100	B3	ESVB30G107M	4	20	1.3	38	22	±15%	±15%
	100	B2	ESVB20G107M	4	12	0.8	22	14	±12%	±12%
	100	C2	ESVC20G107M	4	10	0.8	18	12	±12%	±12%
	150	B2	ESVB20G157M	6	18	0.7	34	20	±12%	±12%
	150	C2	ESVC20G157M	6	10	0.8	18	12	±12%	±12%
	220	B2	ESVB20G227M	8.8	18	0.5	34	20	±12%	±12%
	220	С	ESVC0G227M	8.8	12	0.6	22	14	±12%	±12%
	330 330	C V	ESVC0G337M ESVV0G337M	13.2 13.2	14 12	0.2	26 18	16 14	±12% ±12%	±12% ±12%
	470	D	ESVD0G337M ESVD0G477M	18.8	16	0.5	30	18	±12% ±12%	±12% ±12%
	680	D	ESVD0G687M	27.2	24	0.3	46	26	±12%	±12%
	1.5	P	ESVP0J155M	0.5	10	25	15	15	±20%	±20%
	2.2	J	ESVJ0J225M	0.5	20	17.5	30	30	±20%	±20%
	3.3	J	ESVJ0J335M	0.5	20	13.5	30	30	±20%	±20%
	4.7	J	ESVJ0J475M	0.5	20	8.5	30	30	±20%	±20%
	4.7	Р	ESVP0J475M	0.5	20	10	30	30	±20%	±20%
	4.7	A	ESVA0J475M	0.5	8	5.5	12	10	± 5%	±10%
	6.8	J	ESVJ0J685M	0.5	20	7	30	30	±20%	±20%
6.3	6.8 6.8	P A2	ESVP0J685M ESVA20J685M	0.5 0.5	20 8	7 6.5	30 12	10	±20% ±12%	±20% ±12%
	10	J	ESVJ0J106M	0.5	20	8	38	22	±20%	±20%
	10	P	ESVP0J106M	0.6	20	6	30	30	±20%	±20%
	10	A2	ESVA20J106M	0.6	8	4.5	12	10	±12%	±12%
	10	А	ESVA0J106M	0.6	8	3.2	12	10	±12%	±12%
	15	Р	ESVP0J156M	0.9	20	5	30	30	±20%	±20%
	15	A2	ESVA20J156M	0.9	12	4	22	14	±12%	±12%
	15	Α	ESVA0J156M	0.9	8	3	12	10	±12%	±12%

Rated	0	•	Part	Leakage			DF	(%)	Capaci	tance
Voltage (V)	Capacitance (μF)	Case Code	Number (Bulk)	Current (μA)	DF (%)	ESR (Ω)	−55°C	+125°C	Change 1	Change 2
	22	Р	ESVP0J226M	1.3	20	4	38	22	±20%	±20%
	22	A2	ESVA20J226M	1.3	12	2.8	22	14	±12%	±12%
	22	A	ESVA0J226M	1.3	10	3	14	12	±12%	±12%
	22 22	B3 B2	ESVB30J226M	1.3 1.3	8	2	12 12	10 10	±15%	±15%
	33	A A	ESVB20J226M ESVA0J336M	2	12	1.6 2.5	22	14	± 5% ±12%	±10% ±12%
	33	B3	ESVB30J336M	2	12	1.7	18	15	±15%	±15%
	47	A	ESVA0J476M	2.9	12	2	22	14	±12%	±12%
	47	В3	ESVB30J476M	2.9	12	1.7	18	15	±15%	±15%
	47	B2	ESVB20J476M	2.9	8	1.3	12	10	± 5%	±10%
6.3	47	С	ESVC0J476M	2.9	8	0.9	12	10	± 5%	±10%
	68	B2	ESVB20J686M	4.2	10	1	18	12	±12%	±12%
	68 100	C2 B2	ESVC20J686M ESVB20J107M	4.2 6.3	10 12	0.8	14 22	12 14	±12% ±12%	±12% ±12%
	100	C2	ESVC20J107M	6.3	10	0.9	14	12	±12%	±12%
	100	C	ESVC0J107M	6.3	10	0.6	14	12	±12%	±12%
	150	С	ESVC0J157M	9.4	10	0.6	18	12	±12%	±12%
	220	С	ESVC0J227M	13.8	14	1.2	26	16	±12%	±12%
	220	V	ESVV0J227M	13.8	12	0.5	18	14	±12%	±12%
	220	D	ESVD0J227M	13.8	12	0.5	18	14	±12%	±12%
	330	D	ESVD0J337M	20.7	14	0.5	26	16	±12%	±12%
	470	D P	ESVD0J477M ESVP1A105M	29.6	20	0.3 25	38 15	22 15	±20%	±20%
	1.5	J	ESVP1A105M ESVJ1A155M	0.5 0.5	10	25.5	30	30	±20% ±20%	±20% ±20%
	1.5	P	ESVJ1A155M	0.5	20	25.5	30	30	±20% ±20%	±20% ±20%
	2.2	J	ESVJ1A225M	0.5	20	17.5	30	30	±20%	±20%
	2.2	P	ESVP1A225M	0.5	20	19	30	30	±20%	±20%
	3.3	Р	ESVP1A335M	0.5	20	13	30	30	±20%	±20%
	3.3	A2	ESVA21A335M	0.5	8	8	12	10	±12%	±12%
	4.7	J	ESVJ1A475M	0.5	20	10	30	30	±20%	±20%
	4.7	P	ESVP1A475M	0.5	20	6	30	30	±20%	±20%
	4.7 4.7	A2 A	ESVA21A475M ESVA1A475M	0.5 0.5	8	8 4.5	12 12	10 10	±12% ±12%	±12% ±12%
	6.8	A2	ESVA1A473M ESVA21A685M	0.6	8	8	12	10	±12%	±12%
	6.8	A	ESVA1A685M	0.6	8	4.5	12	10	±12%	±12%
	10	Р	ESVP1A106M	1	20	6	30	30	±20%	±20%
	10	A2	ESVA21A106M	1	8	8	12	10	±12%	±12%
	10	Α	ESVA1A106M	1	8	3.2	12	10	±12%	±12%
	10	B2	ESVB21A106M	1	8	2.4	12	10	± 5%	±10%
10	15	B3	ESVB31A156M	1.5	8	2.7	12	10	±15%	±15%
	22 22	B3	ESVA1A226M ESVB31A226M	2.2	12 8	2.5 1.9	12	14	±12% ±15%	±12% ±15%
	22	B2	ESVB31A226M	2.2	8	1.9	12	10	± 5%	±10%
	33	B3	ESVB31A336M	1.7	12	1.7	18	15	±15%	±15%
	33	B2	ESVB21A336M	3.3	8	1.4	12	10	± 5%	±10%
	47	B2	ESVB21A476M	4.7	8	1	12	10	±12%	±12%
	47	C2	ESVC21A476M	4.7	8	1	12	10	±12%	±12%
	47	С	ESVC1A476M	4.7	8	0.9	12	10	± 5%	±10%
	68	C2	ESVC21A686M	6.8	10	1	18	14	±12%	±12%
	68 68	B2 C	ESVB21A686M ESVC1A686M	6.8 6.8	12	0.9	14 12	14 10	±12% ±12%	±12% ±12%
	100	C	ESVC1A666W ESVC1A107M	10	10	0.7	18	12	±12%	±12%
	100	V	ESVV1A107M	10	8	0.5	18	10	±12%	±12%
	100	D	ESVD1A107M	10	8	0.6	18	10	± 5%	±10%
	150	V	ESVV1A157M	15	8	0.5	18	10	±12%	±12%
	150	D	ESVD1A157M	15	10	0.6	18	12	±12%	±12%
	220	D	ESVD1A227M	22	12	0.6	22	14	±12%	±12%
	0.47	P	ESVP1C474M	0.5	10	35	15	15	±20%	±20%
	0.68	P .	ESVP1C684M	0.5	10	25	15	15	±20%	±20%
	1	J P	ESVJ1C105M ESVP1C105M	0.5 0.5	10	25.5 20	30 15	15 15	±20% ±20%	±20% ±20%
16	1.5	A	ESVA1C155M	0.5	4	6	8	6	±20% ± 5%	±20% ±10%
10	2.2	P	ESVP1C225M	0.5	10	19	15	15	±20%	±20%
	2.2	A2	ESVA21C225M	0.5	6	10	10	8	±12%	±12%
	2.2	Α	ESVA1C225M	0.5	6	6	10	8	± 5%	±10%
	3.3	A2	ESVA21C335M	0.5	8	7	14	10	±12%	±12%

Rated			Part	Laskana			DF (%)	Capacit	ance
Voltage (V)	Capacitance (μF)	Case Code	Number (Bulk)	Leakage Current (μΑ)	DF (%)	ESR (Ω)	−55°C	+125°C	Change 1	Change 2
	3.3	Α	ESVA1C335M	0.5	6	4.5	10	8	±12%	±12%
	4.7	A2	ESVA21C475M	0.7	8	4.5	14	10	±12%	±12%
	4.7	A	ESVA1C475M	0.7	6	4	10	8	±12%	±12%
	6.8	A	ESVA1C685M	1	6	4	10	8	±12%	±12%
	6.8 10	B3 A	ESVB31C685M ESVA1C106M	1.6	6 8	4.1 3.2	10 12	10	±15% ±12%	±15% ±12%
	10	B3	ESVB31C106M	1.6	8	3.5	14	10	±15%	±15%
	10	B2	ESVB21C106M	1.6	6	2	10	8	± 5%	±10%
	15	B2	ESVB21C156M	2.4	6	2	10	8	± 5%	±10%
16	22	B3	ESVB31C226M	3.5	10	2.2	18	12	±15%	±15%
	22	B2	ESVB21C226M	3.5	6	2.2	10	8	± 5%	±10%
	22	С	ESVC1C226M	3.5	6	1.5	10	8	± 5%	±10%
	33	C2	ESVC21C336M	5.2	6	1.4	10	8	±12%	±12%
	33	С	ESVC1C336M	5.2	6	0.9	10	8	± 5%	±10%
	47	С	ESVC1C476M	7.5	6	0.8	10	8	±12%	±12%
	47	D	ESVD1C476M	7.5	6	0.7	10	8	± 5%	±10%
	68	C	ESVC1C686M	10.8	6	0.7	16 10	10	±12%	±12%
	68 100	D D	ESVD1C686M ESVD1C107M	10.8 16	6 8	0.7	10	10	± 5% ±12%	±10% ±12%
	0.47	A2	ESVD1C107M ESVA21D474M	0.5	6	25	18	8	±12% ± 5%	±12% ±10%
	0.47	A2 A2	ESVA21D474W	0.5	6	15	10	8	± 5%	±10%
	1	A2 A2	ESVA21D084M ESVA21D105M	0.5	6	12	10	8	±12%	±12%
	1.5	A2	ESVA21D155M	0.5	6	7.4	10	8	±12%	±12%
	2.2	Р	ESVP1D225M	0.5	10	8	15	15	±20%	±20%
	2.2	A2	ESVA21D225M	0.5	6	7	10	8	±12%	±12%
	2.2	Α	ESVA1D225M	0.5	6	6	10	8	±12%	±12%
	3.3	Α	ESVA1D335M	0.6	6	5	10	8	±12%	±12%
	3.3	В3	ESVB31D335M	0.6	6	3.9	10	8	±15%	±15%
20	4.7	A2	ESVA21D475M	0.9	15	5	30	20	±15%	±15%
	4.7	A	ESVA1D475M	0.9	6	5	10	8	±12%	±12%
	4.7	B3	ESVB31D475M	0.9	6	3	10	8	±15%	±15%
	4.7 6.8	B2 B2	ESVB21D475M ESVB21D685M	0.9 1.3	6	2.8	10 10	8	± 5% ± 5%	±10% ±10%
	10	B2	ESVB21D065M ESVB21D106M	2	6	2.5	10	8	± 5%	±10%
	15	C	ESVC1D156M	3	6	1.7	10	8	± 5%	±10%
	22	C2	ESVC21D226M	4.4	6	1.4	10	8	±12%	±12%
	22	С	ESVC1D226M	4.4	6	1.4	10	8	± 5%	±10%
	22	D	ESVD1D226M	4.4	6	0.8	10	8	± 5%	±10%
	33	D	ESVD1D336M	6.6	6	0.8	10	8	± 5%	±10%
	47	D	ESVD1D476M	9.4	6	0.7	10	8	± 5%	±10%
	0.47	Α	ESVA1E474M	0.5	4	13	8	6	± 5%	±10%
	0.68	A	ESVA1E684M	0.5	6	9	10	8	± 5%	±10%
	1	P	ESVP1E105M	0.5	6	8	10	8	±20%	±20%
	1	A2 A	ESVA21E105M ESVA1E105M	0.5 0.5	6	13	10	8	±12% ± 5%	±12% ±10%
	2.2	A	ESVA1E105M ESVA1E225M	0.5	6	7	10	8	± 5% ±12%	±10%
25	3.3	A	ESVA1E335M	0.8	6	7	10	8	±12%	±12%
	4.7	B3	ESVB31E475M	1.1	6	3	10	8	±15%	±15%
	4.7	B2	ESVB21E475M	1.1	6	3	10	8	± 5%	±10%
	10	С	ESVC1E106M	2.5	6	1.2	10	8	± 5%	±10%
	15	С	ESVC1E156M	3.7	6	1.5	10	8	±12%	±12%
	22	D	ESVD1E226M	5.5	6	0.8	10	8	± 5%	±10%
	33	D	ESVD1E336M	8.2	6	0.7	10	8	± 5%	±10%
	0.47	A	ESVA1V474M	0.5	6	12	10	8	± 5%	±10%
	0.68	Α Α	ESVA1V684M	0.5	6	8	10	8	± 5%	±10%
	1	A2	ESVA21V105M	0.5	6	13	10	8	±12%	±12%
	1.5	A	ESVA1V105M ESVA1V155M	0.5 0.5	6	7	10 10	8	±12% ±12%	±12% ±12%
	2.2	A	ESVATV 155M ESVATV225M	0.5	6	7	10	8	±12%	±12%
35	2.2	B2	ESVB21V225M	0.7	6	4	10	8	± 5%	±10%
55	3.3	B2	ESVB21V335M	1.1	6	3.5	10	8	± 5%	±10%
	4.7	С	ESVC1V475M	1.6	6	2.2	10	8	± 5%	±10%
	6.8	С	ESVC1V685M	2.3	6	1.3	10	8	± 5%	±10%
	10	С	ESVC1V106M	3.5	6	1.5	10	8	± 5%	±10%
	10	D	ESVD1V106M	3.5	6	1	10	8	± 5%	±10%
	15	D	ESVD1V156M	5.2	6	0.9	10	8	± 5%	±10%

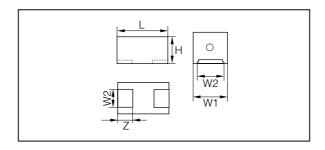
F/SV Series Tantalum Chip Capacitors

New Product

■ FEATURE

- Lead-free type. In conformity to RoHS.
- Face down terminal
- \bullet The low-profile of height 0.9mm Max and large capacitance of 47 μ F available in 1608 size.
- Enable fillet bonding

■ DIMENSIONS



(Unit: mm)

Case Code	L	W 1	W 2	Н	Z
J	1.6±0.1	0.85±0.1	0.65±0.1	0.8±0.1	0.5±0.05
P2 *	2.0±0.1	1.25±0.1	0.9±0.1	0.9±0.1	0.5±0.1
A3 *	3.2±0.2	1.6±0.2	1.2±0.1	0.9±0.1	0.8±0.2

^{*} Under development

■ STANDARD C-V VALUE REFERENCE BY CASE CODE

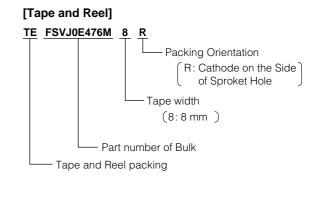
UR :Rated Voltage

	UR	2.5	4	6.3	10	16	20	25
μ F		0E	0G	0J	1A	1C	1D	1E
1							[J]	
1.5								
2.2								[P2]
3.3								
4.7	475					[J]	[P2]	[A3]
6.8	685							
10	106				[J]	[P2]	[A3]	
15	156							
22	226			[J]	[P2]	[A3]		
33	336		J	[P2]				
47	476	J		[P2]	[A3]			
68	686		[P2]					·
100	107	[P2]	[P2]	[A3]				
220	227	[A3]	[A3]					

^{[]:}Under development

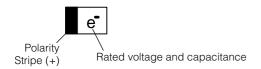
■ PART NUMBER SYSTEM

[Bulk] FSV J OE 476 M Capacitance Tolerance (M: ±20%) Capacitance (in pF) (First two digits represent significant figures. Third digit specifies number of zeros to follow.) Rated voltage Case code

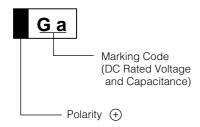


■ MARKINGS

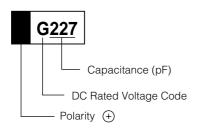
[J case]



[P2 case] Under development



[A3 case] Under development



[Rated voltage and capacitance]

[J case Marking code]

UR :Rated Voltage

•		5	•				
	UR	2.5	4	6.3	10	16	20
μ F		0E	0G	0J	1A	1C	1D
1.0	105						[0-]
1.5	155						
2.2	225						
3.3	335						
4.7	475					[ɔ-]	
6.8	685						
10	106				[⋖ ⁻]		
15	156						
22	226			[J ⁻]			
33	336		G ⁻				
47	476	e ⁻					

[]: Under development

[P2 case Marking code]

UR :Rated Voltage

-		U	•					J
	UR	2.5	4	6.3	10	16	20	25
μ F		0E	0G	0J	1A	1C	1D	1E
2.2	225							EJ
3.3	335							
4.7	475						DS	
6.8	685							
10	106					CĀ		
15	156							
22	226				ΑJ			
33	336			JN				
47	476			JS				
68	686		GW					
100	107	ea	Ga					

[A3 case DC Rated Voltage code]

Code	е	G	J	Α	С	D	E
Rated Voltage	2.5 V	4 V	6.3 V	10 V	16 V	20 V	25 V

■ PERFORMANCE CHARACTERISTICS

Test Conditions: Conform to IEC 60384-1

ITEM				Р	ERFORMAN	CE				TEST CONDITION
Operating tempera	5 1 Dotate Veltage at 50 C at 110					Derate voltage at 85°C at more				
Rated voltage (V.o	dc)	2.5V	4V	[6.3V]	[10V]	[16V]	[20V]	[25V]	at 85°C
Derated voltage (\	V.dc)	1.6V	2.5V	[4V]	[6.3V]	[10V]	[13V]	[16V]	at 125°C
Surge voltage (V.o	dc)	3.3V	5.2V	[8V]	[13V]	[20V]	[26V]	[33V]	at 85°C
Capacitance					33 μF to 47 μ	ιF				
Capacitance tolera	ance				±20%					at 120 Hz
						Voltage: Rated voltage for 5min.				
Dissipation Factor				Refe	r to Standard F	Ratings				at 120 Hz
Equivalent Series	Resistance			Refe	r to Standard F	Ratings				at 100 kHz
	Capacitance change DF(%) L.C									
Surge voltage test Refer to Standard Ratings Refer to Standard Ratings Refer to Standard Ratings Refer to Standard Ratings Lower than initial specification Specification Lower than initial specification Specification Specification Specification Temperature: 85±2°C Applied voltage: Surge voltage voltage is 30 do Duration of surge is 30 do Duration of surge:					Applied voltage: Surge voltage Series resistance: 33 ohm Duration of surge: 30±5 sec Time between surge: 5.5min.					
	-55°C	Not to e	exceed -20%	Refe	r to Standard I	Ratings				Step 1: 25±2°C
Characteristic at high and low temperature	+85°C	Not to e	xceed +20%	ı	ower than init			0.1C•V(μA) which ever is		Step 2: -55.3°C Step 3: 25±2°C
temperature	+125°C	Not to e	xceed +20%	Refe	r to Standard F	Ratings	0.125C•V(μA) or 6.25μA, which ever is greater			Step 4: 125.3°C
Rapid change of temperature		Refer to St	andard Ratinę	ıs	Lower than init			Lower than specifications		Parts shall be temperature cycled over a temperature range of -55 to +125°C, five times continuously as follow. Step 1: -55-3° °C, 30±3min. Step 2: room temp., 10 to 15min. Step 3: 125-3°C, 30±3min. Step 4: room temp, 10 to 15min.
Resistance to Solo heat	dering	Refer to S	tandard Ratin	gs	ower than init			Lower that		solder dip : 260°C, 5sec solder reflow : 260°C, 10sec
Damp heat		Refer to Standard Ratings		gs Lowe	r than 1.5 time specification			Lower that		at 40°C at 90 to 95% RH 500 hour
Endurance		Refer to S	tandard Ratin	gs I	ower than init		ı	Lower than 2 to specifications		at 85°C : Rated voltage at 125°C : Derated voltage 2000 hour
Failure Rate λ0=1% / 1000 hour at 85°C: Rated voltage at 125°C: Derated voltag 2000 hour		at 125°C: Derated voltage								
Terminal Strength			Visual: There s	hall be no	evidence of n	nechanic	al da	amage		Strength: 4.9N Time: 10±0.5sec. (two directions)

[]: Under development

Reference: Derated voltage (85 to 125°C)

$$[U_T] = [U_R] - \frac{[U_R] - [U_C]}{40} (T-85)$$

 $\left[U_{T}\right]$: Derated voltage at operating temperature

[U_R]: Rated voltage

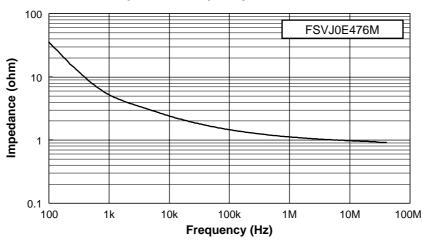
[Uc] : Derated voltage at 125°C T : Ambient temperature

■ RATINGS

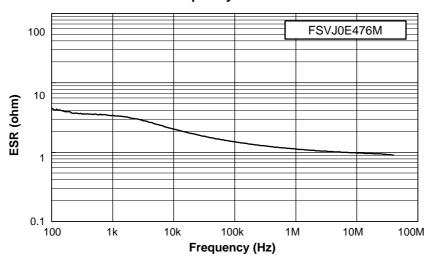
							DF (%	5)	Capac	itance
Rate Voltaç (V)		Case Code	Part Number (Bulk)	Leakage Current (μA)	ent (%)		−55°C	+125°C	Change 1	Change 2
2.5	47	J	FSVJ0E476M	1.1	30	4	60	40	±20%	±20%
4	33	J	FSVJ0G336M	1.3	30	4	60	30	±20%	±20%

■ CHARACTERISTICS (reference)

Impedance-frequency characteristics



ESR-frequency characteristics

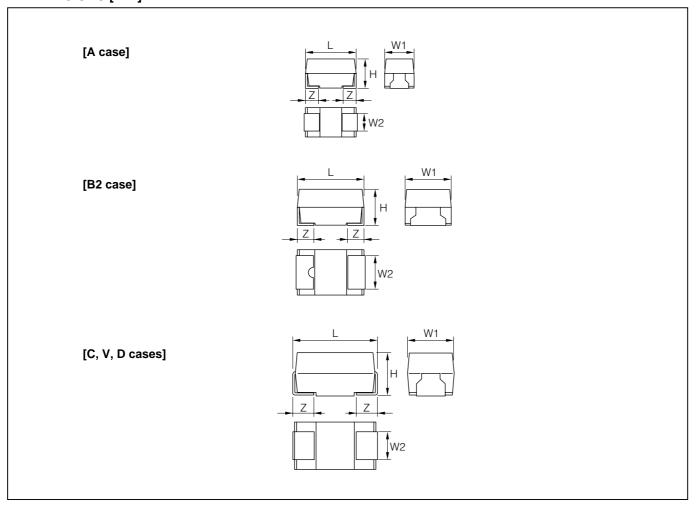


SV/Z Series Tantalum Chip Capacitors (Low-ESR Type)

■ FEATURES

- Lead-free Type. In conformity to RoHS.
- Low-ESR Type.
- For decoupling with CPU, for absorbing the noise.
- Same Dimension as E/SV series.

■ DIMENSIONS [mm]



(Unit: mm)

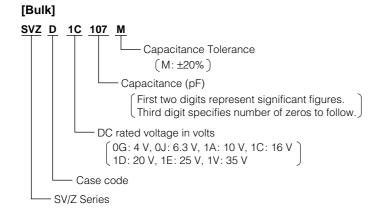
Case Code	EIA code	L	W 1	W ₂	н	Z
А	3216	3.2 ± 0.2	1.6 ± 0.2	1.2 ± 0.1	1.6 ± 0.2	0.8 ± 0.2
B2	3528	3.5 ± 0.2	2.8 ± 0.2	2.2 ± 0.1	1.9 ± 0.2	0.8 ± 0.2
С	6032	6.0 ± 0.2	3.2 ± 0.2	2.2 ± 0.1	2.5 ± 0.2	1.3 ± 0.2
V	7343L	7.3 ± 0.2	4.3 ± 0.2	2.4 ± 0.1	1.9 ± 0.1	1.3 ± 0.2
D	7343	7.3 ± 0.2	4.3 ± 0.2	2.4 ± 0.1	2.8 ± 0.2	1.3 ± 0.2

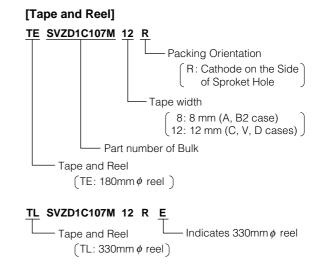
■ STANDARD C-V VALUE REFERENCE BY CASE CODE

	UR	4 V	6.3 V	10 V	16 V	20 V	25 V	35 V
μ F		0G	0J	1A	1C	1D	1E	1V
6.8	685						C 600	C 600
10	106		A 800	B2 600				D 300
15	156						D 250	D 300
22	226		B2 800				D 200	
33	336					D 200		
47	476			C 300	D 150	D 150		
68	686			B2 250	C, D 200, 150			
100	107		C, D 150, 150	C, V, D 125, 150, 100	D 100			
150	157		C, D 125, 100	V, D 150, 100				
220	227	D 100	V, D 150, 100	D 100				
330	337	V, D 150, 100	D 100					

Number : ESR $(m\Omega)$

■ PART NUMBER SYSTEM



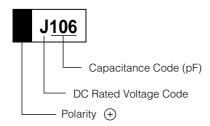


NEC/TOKIN

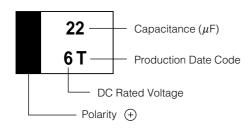
■ MARKINGS

The standard marking shows capacitance, DC rated voltage, and polarity.

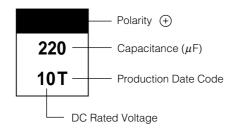
[A case] (ex. $10 \,\mu\text{F} / 6.3 \,\text{V}$)



[B2 case] (ex. $22 \mu F / 6.3 V$)



[C, V, D case] (ex. 220 $\mu\mathrm{F}$ / 10 V)



[DC Rated Voltage code]

Code	G	J	Α	C	D	E	٧
Rated Voltage	4 V	6.3 V	10 V	16 V	20 V	25 V	35V

[B2, C, V, D cases production date code]

YM	Jan.	Feb.	Mar.	Apr.	May	Jun.	Jul.	Aug.	Sep.	Oct.	Nov.	Dec.
2003	а	b	С	d	е	f	g	h	j	k	- 1	m
2004	n	р	q	r	S	t	u	٧	W	х	у	Z
2005	Α	В	С	D	Е	F	G	Н	J	K	L	М
2006	N	Р	Q	R	S	Т	U	V	W	Х	Υ	Z

Note: Production date code will resume beginning in 2007.

■ PERFORMANCE CHARACTERISTICS

Test Conditions: Conform to IEC 60384-1

ITEM				PI	ERFORMAN	CE				TEST CONDITION
Operating tempera	ature			-	55°C to +125°	C				Derate voltage at 85°C at more
Rated voltage (V.o	dc)	4V	6.3V	10V	16V	20V		25V	35V	at 85°C
Derated voltage (\	/.dc)	2.5V	4V	6.3V	10V	13V		16V	22V	at 125°C
Surge voltage (V.c	ic)	5.2V	8V	13V	V 20V 26V			33V	46V	at 85°C
Capacitance		6.8 μF to 330 μF								-1.400 -
Capacitance tolera	ance				±20% or ±10%	%				at 120 Hz
DC Leakage Current (L.C)		0.01C • V(μA) or 0.5μA , whichever is greater							Voltage: Rated voltage for 5min.	
Dissipation Factor				Refer	to Standard F	Ratings				at 120 Hz
Equivalent Series	Resistance			Refer	to Standard F	Ratings				at 100 kHz
		Capacita	ance change		DF(%)			L.C		
Surge voltage test		Refer to St	andard Rating	S L	ower than init			Lower than specificate		Temperature: 85±2°C Applied voltage: Surge voltage Series resistance: 33 ohm Duration of surge: 30±5 sec Time between surge: 5.5min. Number of cycle: 1000
	-55°C	Not to e	exceed -12%	Refer	Refer to Standard Ratings					Oham 4, 05 000
Characteristic at high and low temperature	+85°C	Not to e	xceed +12%	L	ower than init			0.1C • V(μA) which ever is		Step 1: 25±2°C Step 2: -55,3°C Step 3: 25±2°C
temperature	+125°C	Not to e	xceed +15%	Refer	Refer to Standard Ratings			25C • V(μA) which ever is		Step 4: 125.3°C
Rapid change of temperature		Refer to St	andard Rating	S L	ower than init			Lower than specifica		Parts shall be temperature cycled over a temperature range of -55 to +125°C, five times continuously as follow. Step 1: -55.3°C, 30±3min. Step 2: room temp., 10 to 15min. Step 3: 125.3°C, 30±3min. Step 4: room temp, 10 to 15min.
Resistance to Solo heat	dering	Refer to S	tandard Rating	s L	ower than init			Lower than		solder dip : 260°C, 5sec solder reflow : 260°C, 10sec
Damp heat		Refer to S	tandard Rating	s Lower	than 1.25 time specification			Lower than		at 40°C at 90 to 95% RH 500 hour
Endurance		Refer to S	tandard Rating	s	Lower than initial specification		Lower than 1.25 times initial specification			at 85°C : Rated voltage at 125°C : Derated voltage 2000 hour
Failure Rate		λο = 1% / 1000 hour						at 85°C : Rated voltage at 125°C : Derated voltage 2000 hour		
Terminal Strength		Visual: There shall be no evidence of mechanical damage						Strength: 4.9N Time: 10±0.5sec. (two directions)		

Reference: Derated voltage (85 to 125°C)

$$[U_T] = [U_R] - \frac{[U_R] - [U_C]}{40} (T-85)$$

 $[U_T]$: Derated voltage at operating temperature

[U_R]: Rated voltage

[Uc] : Derated voltage at 125°C T : Ambient temperature

NEC/TOKIN

■ STANDARD RATINGS

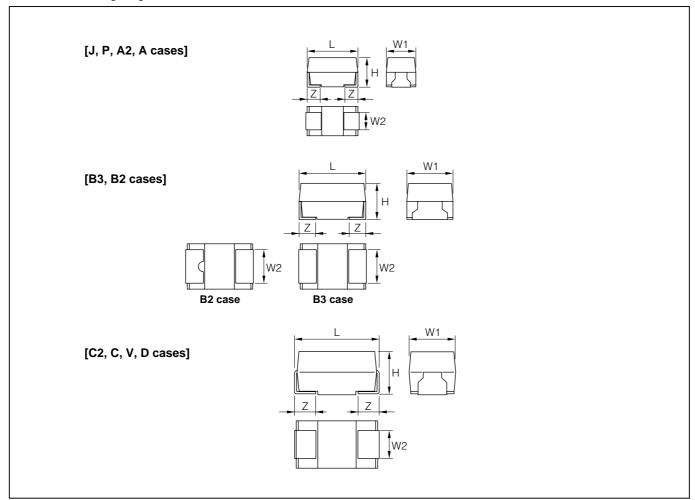
							DF	(%)	Capaci	tance
Rated Voltage (V)	Capacitance (μF)	Case Code	Part Number (Bulk)	Leakage Current (μA)	DF (%)	ESR (mΩ)	–55°C	+125°C	Change 1	Change 2
	220	D	SVZD0G227M	8.8	8	100	18	10	± 5%	± 5%
4	330	V	SVZV0G337M	13.2	12	150	18	14	±12%	±12%
	330	D	SVZD0G337M	13.2	14	100	18	16	±12%	±12%
	10	Α	SVZA0J106M	0.6	8	800	12	10	±12%	±12%
	22	B2	SVZB20J226M	1.3	8	800	12	10	± 5%	± 5%
	100	С	SVZC0J107M	6.3	10	150	14	12	±12%	±12%
İ	100	D	SVZD0J107M	6.3	8	150	12	10	± 5%	± 5%
6.3	150	С	SVZC0J157M	9.4	10	125	18	12	±12%	±12%
	150	D	SVZD0J157M	9.4	8	100	18	10	± 5%	± 5%
ĺ	220	V	SVZV0J227M	13.8	12	150	18	14	±12%	±12%
İ	220	D	SVZD0J227M	13.8	12	100	18	14	±12%	±12%
	330	D	SVZD0J337M	20.7	14	100	26	16	±12%	±12%
	10	B2	SVZB21A106M	1	8	600	12	10	± 5%	± 5%
	47	С	SVZC1A476M	4.7	8	300	12	10	± 5%	± 5%
İ	68	B2	SVZB21A686M	6.8	12	250	14	14	±12%	±12%
	100	С	SVZC1A107M	10	10	125	18	12	±12%	±12%
10	100	V	SVZV1A107M	10	8	150	18	10	±12%	±12%
	100	D	SVZD1A107M	10	8	100	18	10	± 5%	± 5%
	150	V	SVZV1A157M	15	8	150	14	10	±12%	±12%
İ	150	D	SVZD1A157M	15	10	100	18	12	±12%	±12%
ĺ	220	D	SVZD1A227M	22	12	100	22	14	±12%	±12%
	47	D	SVZD1C476M	7.5	6	150	10	8	± 5%	± 5%
	68	С	SVZC1C686M	10.8	6	200	16	10	±12%	±12%
16	68	D	SVZD1C686M	10.8	6	150	10	8	± 5%	± 5%
İ	100	D	SVZD1C107M	16	8	100	18	10	±12%	±12%
20	33	D	SVZD1D336M	6.6	6	200	10	8	± 5%	± 5%
20	47	D	SVZD1D476M	9.4	6	150	10	8	± 5%	± 5%
	6.8	С	SVZC1E685M	1.7	6	600	10	8	± 5%	± 5%
25	15	D	SVZD1E156M	3.7	6	250	10	8	± 5%	± 5%
	22	D	SVZD1E226M	5.5	6	200	10	8	± 5%	± 5%
	6.8	С	SVZC1V685M	2.3	6	600	10	8	± 5%	± 5%
35	10	D	SVZD1V106M	3.5	6	300	10	8	± 5%	± 5%
	15	D	SVZD1V156M	5.2	6	300	10	8	± 5%	± 5%

PS/L Series NeoCapacitor CONDUCTIVE POLYMER TANTALUM CAPACITORS

■ FEATURES

- Lead-free Type. In conformity to RoHS.
- Ultra-Low ESR
- Same Dimension as E/SV series

■ DIMENSIONS [mm]



(Unit: mm)

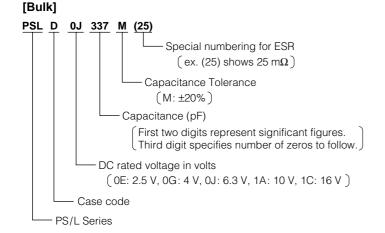
Case Code	EIA code	L	W 1	W ₂	н	z
J	-	1.6 ± 0.1	0.8 ± 0.1	0.6 ± 0.1	0.8 ± 0.1	0.3 ± 0.15
Р	2012	2.0 ± 0.2	1.25 ± 0.2	0.9 ± 0.1	1.1 ± 0.1	0.5 ± 0.1
A2 (U)	3216L	3.2 ± 0.2	1.6 ± 0.2	1.2 ± 0.1	1.1 ± 0.1	0.8 ± 0.2
Α	3216	3.2 ± 0.2	1.6 ± 0.2	1.2 ± 0.1	1.6 ± 0.2	0.8 ± 0.2
B3 (W)	3528L	3.5 ± 0.2	2.8 ± 0.2	2.2 ± 0.1	1.1 ± 0.1	0.8 ± 0.2
B2 (S)	3528	3.5 ± 0.2	2.8 ± 0.2	2.2 ± 0.1	1.9 ± 0.2	0.8 ± 0.2
C2	_	6.0 ± 0.2	3.2 ± 0.2	2.2 ± 0.1	1.4 ± 0.1	1.3 ± 0.2
С	6032	6.0 ± 0.2	3.2 ± 0.2	2.2 ± 0.1	2.5 ± 0.2	1.3 ± 0.2
V	7343L	7.3 ± 0.2	4.3 ± 0.2	2.4 ± 0.1	1.9 ± 0.1	1.3 ± 0.2
D	7343	7.3 ± 0.2	4.3 ± 0.2	2.4 ± 0.1	2.8 ± 0.2	1.3 ± 0.2

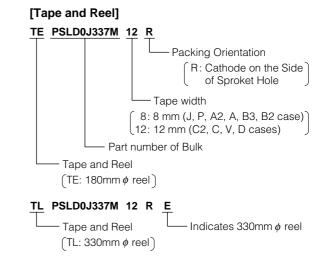
■ STANDARD C-V VALUE REFERENCE BY CASE CODE

	UR	2.5 V	4V	6.3V	10V	16V	20V
μ F		0E	0G	0J	1A	1C	1D
2.2	225			J	J		
3.3	335			J, P	A	A	
4.7	475			J, P	A2, A	B2	
6.8	685			P, A	A, B2	B2	
10	106		J, P, A	P, A2, A	A2, A, B2	B2	
15	156			A2, A, B2	B2, C		
22	226	P	P, A2, B2	A2, A, B3, B2	B3, B2, C	[C2(70)]	[V(80]
33	336		A	A, B3, B2	B3, B2, C2, C	[V(70)]	[V(80)]
47	476		A, B3	B3, B2, C2, C	B2, C2, C, V, D	D, [V(70)]	
68	686		C2, C	B2, C2, C	V, D, [C(100/55)]		
100	107	В3	B3, B2, C2	B2, C, [C2(70)]	V, D, [C(100/55)]		
150	157		B2, C	C, V, D, [C(18)]	D		
220	227	B2	C, V, D, [B2(45)]	V, D	D		
330	337	C, V, [B2(45)], V, [C(18)]	C, V, D	D			
470	477	V	D				
680	687	D	D				
1000	108	D					

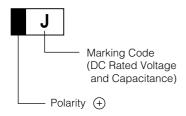
^{[] :}Under development-specification to be determined. Numeral : ESR (m Ω) at 100kHz

■ PART NUMBER SYSTEM

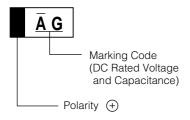




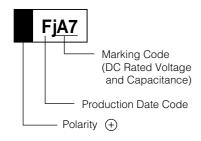
[J case] (ex. $4.7 \mu F / 6.3 V$)



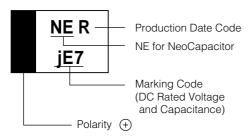
[P case] (ex. $10 \,\mu\text{F} / 4 \,\text{V}$)



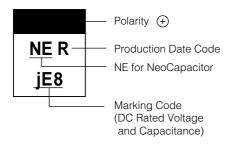
[A2, A cases] (ex. $10 \,\mu\text{F} / 6.3 \,\text{V})$



[B3, B2 cases] (ex. 15 μ F / 6.3 V)



[C2, C, D cases] (ex. 150 μ F / 6.3 V)



[J case Marking Code]

μ F	4 V	6.3 V	10 V
2.2		ſ	<
3.3		7	
4.7		J	
6.8			
10	9		

[P case Marking Code]

μ F U^R	2.5V	4 V	6.3 V	10 V
3.3			NJ	
4.7			SJ	
6.8			WJ	
10		ĀG	ĀJ	
15				
22	Je	JG		

[A2, A, B3, B2, C2, C, V, D cases Marking Code]

μ F	UR	2.5 V	4 V	6.3 V	10 V	16 V	20V
		е	g	j	Α	С	D
3.3	N6				AN6	CN6	
4.7	S6				AS6	CS6	
6.8	W6			jW6	AW6	CW6	
10	A7		gA7	jA7	AA7	CA7	
15	W7			jE7	AE7		
22	J7		gJ7	jJ7	AJ7		[DJ7]
33	N7		gN7	jN7	AN7		[DN7]
47	S7		gS7	jS7	AS7	CS7	
68	W7		gW7	jW7	AW7		
100	A8	eA8	g A8	jA8	AA8		
150	E8		gE8	jE8	AE8		
220	J8	eJ8	gJ8	jJ8	AJ8		
330	N8	eN8	gN8	jN8			
470	S8	eS8	gS8				
680	W8	eW8	gW8				
1000	A9	eA9					

[]: Under development

[A2, A, B3, B2, C2, C, V, D cases production date code]

YM	Jan.	Feb.	Mar.	Apr.	Мау	Jun.	Jul.	Aug.	Sep.	Oct.	Nov.	Dec.
2003	а	b	С	d	е	f	g	h	j	k		m
2004	n	р	q	r	S	t	u	٧	w	Х	у	z
2005	Α	В	С	D	Е	F	G	Н	J	K	L	М
2006	N	Р	Q	R	S	Т	U	V	W	Х	Υ	Z

Note: Production date code will resume beginning in 2007.

■ PERFORMANCE CHARACTERISTICS

Test Conditions: Conform to IEC 60384-1

ITEM				PERFOR	MANCE			TEST CONDITION
Operating tempera	ture			-55°C to	+105°C			Derate voltage at 85°C at more
Rated voltage (V.d	c)	2.5V	4V	6.3V	10V	16V	[20V]	at 85°C
Derated voltage (V	.dc)	2V	3.3V	5V	8V	12.8V	[16V]	at 105°C
Surge voltage (V.de	c)	3.3V	5.2V	8V	13V	20V	[26V]	at 85°C
Capacitance				2.2 μF to	1000 μF			at 120 Hz
Capacitance tolera	nce			±20	0%			at 120112
DC Leakage Curre	nt (L.C)		0.1C • V(μA) o	or 3μA (J case:	10μA) , whiche	ever is greater		Voltage: Rated voltage for 5min.
Dissipation Factor				Refer to Stan	dard Ratings			at 120 Hz
Equivalent Series F	Resistance			Refer to Stan	dard Ratings			at 100 kHz
		Capacitan	ce change	DF((%)	L.	С	
Surge voltage test		Refer to Stan	dard Ratings	Lower th specifi			an initial ication	Temperature: 85±2°C Applied voltage: Surge voltage Series resistance: 33 ohm Duration of surge: 30±5 sec Time between surge: 5.5min. Number of cycle: 1000
Characteristic -55°C		from 0 to -	-20%	Lower th specifi				Step 1: 25±2°C Step 2: -55.3°C
at high and low temperature +105°C		from 0 to +	50%	Lower than initial spe		Lower tha initial spe	n 10 times ecification	Step 3: 25±2°C Step 4: 105.3°C
Rapid change of temperature		Refer to Standard Ratings		Lower than initial specification			an initial ication	Parts shall be temperature cycled over a temperature range of -55 to +105°C, five times continuously as follow. Step 1: -55.3° °C, 30±3min. Step 2: room temp., 10 to 15min. Step 3: 105.3°C, 30±3min. Step 4: room temp, 10 to 15min.
Resistance to Sold heat	ering	Refer to Star	ndard Ratings	Lower than 1. specifi		Lower th	an initial ication	Reflow soldering method 240°C, 10 sec.Max.
Damp heat		from +30% to	o -20%	Lower than 1. specifi			an initial ication	at 40°C at 90 to 95% RH 500 hour
Endurance I		Refer to Star	ndard Ratings	Lower than 1.5 times initial specification		Lower than initial specification		at 85°C at rated voltage 1000 hour
Endurance II		Refer to Star	ndard Ratings	Lower than 3 specifi			ian initial ication	at 105°C at Derated voltage 1000 hour
Failure Rate				λο = 1% /	1000 hour		at 85°C: rated voltage at 105°C: derated voltage	
Terminal Strength		Visual: There shall b	e no evidence	of mechanical	damage	Strength : 4.9N Time : 10±0.5sec. (two directions)		
Permissible ripple	current	Refer to Rati	ngs Table	-	-	-	-	at 100 kHz
Other		Conform to II	EC60384-1	Conform to IEC60384-1				

Reference : Derated voltage (85 to 125°C)

$$[U_T] = [U_R] - \frac{[U_R] - [U_C]}{20} (T-85)$$

 $[U_T]$: Derated voltage at operating temperature

 $[U_R]: Rated\ voltage$

[Uc] : Derated voltage at 105°C T : Ambient temperature

[]: Under development

■ STANDARD RATINGS

Datad			D1	11			Permissible	DF	(%)	Capac	citance
Rated Voltage (V)	Capacitance (μF)	Case Code	Part Number (Bulk)	Leakage Current (μA)	DF (%)	ESR (mΩ)	Ripple Current (mA rms.)	–55°C	+105°C	Change 1	Change 2
	22	Р	PSLP0E226M	5.5	6	200	354	6	9	±20%	±20%
	100	В3	PSLB30E107M	25	8	70	1035	8	12	±20%	±20%
	220	B2	PSLB20E227M	55	8	45	1374	8	12	±20%	±20%
	220	B2	PSLB20E227M(35)	55	8	35	1558	8	12	±20%	±20%
	330	С	PSLC0E337M(25)	82.5	10	25	2345	10	15	±20%	±20%
	330	V	PSLV0E337M	82.5	10	25	2236	10	15	±20%	±20%
	330	V	PSLV0E337M(15)	82.5	10	15	2887	10	15	±20%	±20%
2.5	330	V	PSLV0E337M(12)	82.5	10	12	3227	10	15	±20%	±20%
	470	V	PSLV0E477M(15)	117.5	10	15	2887	10	15	±20%	±20%
	470	V	PSLV0E477M(12)	117.5	10	12	3227	10	15	±20%	±20%
	680	D	PSLD0E687M	170	10	25	2449	10	15	±20%	±20%
	680	D	PSLD0E687M(15)	170	10	15	3162	10	15	±20%	±20%
	680	D	PSLD0E687M(12)	170	10	12	3536	10	15	±20%	±20%
	1000	D	PSLD0E108M	250	10	25	2449	10	15	±20%	±20%
	1000	D	PSLD0E108M(15)	250	10	15	3162	10	15	±20%	±20%
	10	J	PSLJ0G106M	10	4	300	183	4	6	±20%	±20%
	10	P	PSLP0G106M	4	6	200	354	6	9	±20%	±20%
	10	A	PSLA0G106M	4	6	200	612	6	9	±20%	±20%
	22	P	PSLP0G226M	8.8	6	200	354	6	9	±20%	±20%
	22	A2	PSLA20G226M	8.8	6	200	548	6	9	±20%	±20%
	22	B2	PSLB20G226M	8.8	8	150	753	8	12	±20%	±20%
	33	A	PSLA0G336M	13.2	6	180	645	6	9	±20%	±20%
	47	A	PSLA0G476M	18.8	6	180	645	6	9	±20%	±20%
	47	B3	PSLB30G476M	18.8	8	70	1035	8	12	±20%	±20%
	68	C2	PSLC20G686M	27.2	8	55	1279	8	12	±20%	±20%
	68	С	PSLC0G686M	27.2	9	100	1049	9	14	±20%	±20%
	100 100	B3 B2	PSLB30G107M	40 40	8	70 70	1035 1102	8	12 12	±20% ±20%	±20% ±20%
	100	B2	PSLB20G107M	40	8		1374	8	12	±20%	±20% ±20%
	100	C2	PSLB20G107M(45) PSLC20G107M	40	9	45 55	1279	9	14	±20%	±20% ±20%
	150	B2	PSLB20G157M	60	8	45	1374	8	12	±20%	±20%
	150	B2	PSLB20G157M(35)	60	8	35	1558	8	12	±20%	±20%
	150	C	PSLC0G157M	60	9	100	1049	9	14	±20%	±20%
	220	С	PSLC0G137M	88	9	55	1414	9	14	±20%	±20%
	220	С	PSLC0G227M(45)	88	9	45	1563	9	14	±20%	±20%
	220	С	PSLC0G227M(25)	88	9	25	2098	9	14	±20%	±20%
	220	V	PSLV0G227M	88	10	45	1667	10	15	±20%	±20%
4	220	V	PSLV0G227M(25)	88	10	25	2236	10	15	±20%	±20%
•	220	V	PSLV0G227M(18)	88	10	18	2635	10	15	±20%	±20%
	220	V	PSLV0G227M(15)	88	10	15	2887	10	15	±20%	±20%
	220	V	PSLV0G227M(12)	88	10	12	3227	10	15	±20%	±20%
	220	D	PSLD0G227M	88	10	55	1651	10	15	±20%	±20%
	220	D	PSLD0G227M(40)	88	10	40	1936	10	15	±20%	±20%
	220	D	PSLD0G227M(25)	88	10	25	2449	10	15	±20%	±20%
	220	D	PSLD0G227M(15)	88	10	15	3162	10	15	±20%	±20%
	220	D	PSLD0G227M(12)	88	10	12	3536	10	15	±20%	±20%
	330	С	PSLC0G337M	132	10	55	1414	10	15	±20%	±20%
	330	V	PSLV0G337M	132	10	45	1667	10	15	±20%	±20%
	330	V	PSLV0G337M(25)	132	10	25	2887	10	15	±20%	±20%
	330	V	PSLV0G337M(12)	132	10	12	3227	10	15	±20%	±20%
	330	D	PSLD0G337M	132	10	40	1936	10	15	±20%	±20%
	330	D	PSLD0G337M(25)	132	10	25	2449	10	15	±20%	±20%
	330	D	PSLD0G337M(15)	132	10	15	3162	10	15	±20%	±20%
	470	D	PSLD0G477M	188	10	25	2449	10	15	±20%	±20%
	470	D	PSLD0G477M(18)	188	10	18	2887	10	15	±20%	±20%
	470	D	PSLD0G477M(15)	188	10	15	3162	10	15	±20%	±20%
	470	D	PSLD0G477M(12)	188	10	12	3536	10	15	±20%	±20%
	680	D	PSLD0G687M	272	10	25	2449	10	15	±20%	±20%
	680	D	PSLD0G687M(15)	272	10	15	3162	10	15	±20%	±20%
	680	D	PSLD0G687M(12)	272	10	12	3536	10	15	±20%	±20%

Datad			Part	Leakage			Permissible	DF	(%)	Capacitance		
Rated Voltage (V)	Capacitance (μF)	Case Code	Number (Bulk)	Current (μA)	DF (%)	ESR (mΩ)	Ripple Current (mA rms.)	–55°C	+105°C	Change 1	Change 2	
	2.2	J	PSLJ0J225M	10	4	500	141	4	6	±20%	±20%	
	3.3	J	PSLJ0J335M	10	4	500	141	4	6	±20%	±20%	
	3.3	Р	PSLP0J335M	3	6	300	289	6	9	±20%	±20%	
	4.7	J	PSLJ0J475M	10	4	500	141	4	6	±20%	±20%	
	4.7	Р	PSLP0J475M	3	6	300	289	6	9	±20%	±20%	
	6.8	Р	PSLP0J685M	4.2	6	300	289	6	9	±20%	±20%	
	6.8	Α	PSLA0J685M	4.2	6	300	500	6	9	±20%	±20%	
	10	P	PSLP0J106M	6.3	6	200	354	6	9	±20%	±20%	
	10	A2	PSLA20J106M	6.3	6	200	548	6	9	±20%	±20%	
	10	A	PSLA0J106M	6.3	6	200	612	6	9	±20%	±20%	
	15	A2	PSLA20J156M	9.4	6	200	548	6	9	±20%	±20%	
	15	A	PSLA0J156M	9.4	6	200	612	6	9	±20%	±20%	
	15	B2	PSLB20J156M	9.4	8	150	753	8	12	±20%	±20%	
	22	A2	PSLA20J226M	13.8	6	200	548	6	9	±20%	±20%	
	22 22	A B3	PSLA0J226M PSLB30J226M	13.8 13.8	6	180 70	645 1035	6 8	9 12	±20% ±20%	±20% ±20%	
	22	B3	PSLB30J226M PSLB20J226M		8	150	753		12	±20% ±20%	±20% ±20%	
	33	A A	PSLB20J226M PSLA0J336M	13.8 20.7	8	180	753 645	8	9	±20% ±20%	±20% ±20%	
	33	B3	PSLB30J336M PSLB30J336M	20.7	8	70	1035	8	12	±20% ±20%	±20% ±20%	
	33	B3 B2	PSLB30J336M PSLB20J336M	20.7	8	150	753	8	12	±20% ±20%	±20% ±20%	
	47	B3	PSLB30J476M	29.6	8	70	1035	8	12	±20%	±20%	
	47	B2	PSLB20J476M	29.6	8	150	753	8	12	±20%	±20%	
	47	B2	PSLB20J476M(70)	29.6	8	70	1102	8	12	±20%	±20%	
	47	C2	PSLC20J476M(70)	29.6	9	70	1134	9	14	±20%	±20%	
	47	C	PSLC0J476M	29.6	9	100	1049	9	14	±20%	±20%	
6.3	68	B2	PSLB20J686M	42.8	8	70	1102	8	12	±20%	±20%	
	68	B2	PSLB20J686M(55)	42.8	8	55	1243	8	12	±20%	±20%	
	68	C2	PSLC20J686M	42.8	9	55	1279	9	14	±20%	±20%	
	68	C	PSLC0J686M	42.8	9	100	1049	9	14	±20%	±20%	
	100	B2	PSLB20J107M	63	8	70	1102	8	12	±20%	±20%	
	100	B2	PSLB20J107M(45)	63	8	45	1374	8	12	±20%	±20%	
	100	B2	PSLB20J107M(35)	63	8	35	1558	8	12	±20%	±20%	
	100	С	PSLC0J107M	63	9	100	1049	9	14	±20%	±20%	
	150	С	PSLC0J157M	94.5	9	100	1049	9	14	±20%	±20%	
	150	С	PSLC0J157M(55)	94.5	9	55	1414	9	14	±20%	±20%	
	150	С	PSLC0J157M(45)	94.5	9	45	1563	9	14	±20%	±20%	
	150	С	PSLC0J157M(25)	94.5	9	25	2098	9	14	±20%	±20%	
	150	V	PSLV0J157M	94.5	10	45	1667	10	15	±20%	±20%	
	150	V	PSLV0J157M(25)	94.5	10	25	2236	10	15	±20%	±20%	
	150	V	PSLV0J157M(18)	94.5	10	18	2635	10	15	±20%	±20%	
	150	D	PSLD0J157M	94.5	10	55	1651	10	15	±20%	±20%	
	150	D	PSLD0J157M(40)	94.5	10	40	1936	10	15	±20%	±20%	
	150	D	PSLD0J157M(25)	94.5	10	25	2449	10	15	±20%	±20%	
	220	V	PSLV0J227M	138.6	10	45	1667	10	15	±20%	±20%	
	220	V	PSLV0J227M(15)	138.6	10	15	2887	10	15	±20%	±20%	
	220	V	PSLV0J227M(12)	138.6	10	12	3536	10	15	±20%	±20%	
	220	D	PSLD0J227M	138.6	10	55	1651	10	15	±20%	±20%	
	220	D	PSLD0J227M(40)	138.6	10	40	1936	10	15	±20%	±20%	
	330	D	PSLD0J337M	207.9	10	40	1936	10	15	±20%	±20%	
	330	D	PSLD0J337M(25)	207.9	10	25	2449	10	15	±20%	±20%	
	2.2	J	PSLJ1A225M	10	4	500	141	4	6	±20%	±20%	
	3.3	Α	PSLA1A335M	3.3	6	300	500	6	9	±20%	±20%	
	4.7	A2	PSLA21A475M	4.7	6	300	447	6	9	±20%	±20%	
	4.7	Α	PSLA1A475M	4.7	6	300	500	6	9	±20%	±20%	
10	6.8	Α	PSLA1A685M	6.8	6	300	500	6	9	±20%	±20%	
	6.8	B2	PSLB21A685M	6.8	8	200	652	8	12	±20%	±20%	
	10	A2	PSLA21A106M	10	6	200	548	6	9	±20%	±20%	
	10	Α	PSLA1A106M	10	6	200	612	6	9	±20%	±20%	
	10	B2	PSLB21A106M	10	8	200	652	8	12	±20%	±20%	

D-1-1			Dont	Laslana			Permissible	DF	(%)	Capac	citance
Rated Voltage (V)	Capacitance (μF)	Case Code	Part Number (Bulk)	Leakage Current (μA)	DF (%)	ESR (mΩ)	Ripple Current (mA rms.)	–55°C	+105°C	Change 1	Change 2
	15	B2	PSLB21A156M	15	8	150	753	8	12	±20%	±20%
	15	С	PSLC1A156M	15	9	200	742	9	14	±20%	±20%
	22	В3	PSLB31A226M	22	8	70	1035	8	12	±20%	±20%
	22	B2	PSLB21A226M	22	8	150	753	8	12	±20%	±20%
	22	С	PSLC1A226M	22	9	150	856	9	14	±20%	±20%
	33	В3	PSLB31A336M	33	8	70	1035	8	12	±20%	±20%
	33	B2	PSLB21A336M	33	8	150	753	8	12	±20%	±20%
	33	C2	PSLC21A336M	33	9	70	1134	9	14	±20%	±20%
	33	С	PSLC1A336M	33	9	100	1049	9	14	±20%	±20%
	47	B2	PSLB21A476M	47	8	70	1102	8	12	±20%	±20%
	47	C2	PSLC21A476M	47	9	70	1134	9	14	±20%	±20%
	47	С	PSLC1A476M	47	9	100	1049	9	14	±20%	±20%
10	47	С	PSLC1A476M(55)	47	9	55	1414	9	14	±20%	±20%
	47	V	PSLV1A476M	47	10	60	1443	10	15	±20%	±20%
	47	D	PSLD1A476M	47	10	100	1225	10	15	±20%	±20%
	68	V	PSLV1A686M	68	10	60	1443	10	15	±20%	±20%
	68	D	PSLD1A686M	68	10	100	1225	10	15	±20%	±20%
	100	V	PSLV1A107M	100	10	45	1667	10	15	±20%	±20%
	100	V	PSLV1A107M(25)	100	10	25	2236	10	15	±20%	±20%
	100	D	PSLD1A107M	100	10	55	1651	10	15	±20%	±20%
	150	D	PSLD1A157M	150	10	55	1651	10	15	±20%	±20%
	150	D	PSLD1A157M(40)	150	10	40	1936	10	15	±20%	±20%
	220	D	PSLD1A227M	220	10	55	1651	10	15	±20%	±20%
	220	D	PSLD1A227M(40)	220	10	40	1936	10	15	±20%	±20%
	220	D	PSLD1A227M(25)	220	10	25	2449	10	15	±20%	±20%
	3.3	Α	PSLA1C335M	5.2	6	800	306	6	9	±20%	±20%
	4.7	B2	PSLB21C475M	7.5	8	200	652	8	12	±20%	±20%
16	6.8	B2	PSLB21C685M	10.8	8	200	652	8	12	±20%	±20%
	10	B2	PSLB21C106M	16	8	100	922	8	12	±20%	±20%
	47	D	PSLD1C476M	75.2	10	70	1464	10	15	±20%	±20%

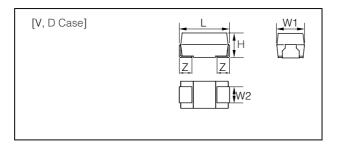
PS/G Series NeoCapacitor

New Product

■ FEATURE

- Lead-free type. In conformity to RoHS.
- Extreme low ESR (7mhom) and excellent noise absorption performance.
- High capacitance and ultra low ESR based upon on our original Conductive Polymer technology.
- Same outer dimension an conventional PS/L series.

■ DIMENSIONS



(Unit: mm)

Case Code	L	W 1	W ₂	н	z
V	7.3± 0.2	4.3 ± 0.2	2.4 ± 0.2	1.9 ± 0.1	1.3 ± 0.2
D	7.3± 0.2	4.3 ± 0.2	2.4 ± 0.2	2.8 ± 0.2	1.3 ± 0.2

■ STANDARD C-V VALUE REFERENCE BY CASE CODE

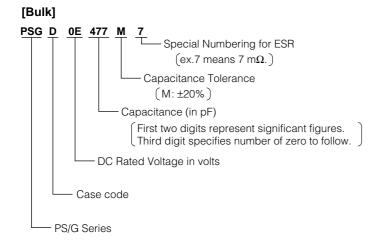
UR :Rated Voltage

	U R	2.5
μ F		0E
220	227	$\begin{bmatrix} V \\ 9 \end{bmatrix}$
330	337	V D 9, [7] 9, 7
470	477	V D 9, 7 9, 7, 6
680	687	D 9, 7

Numeral:ESR (mΩ) at 100kHz

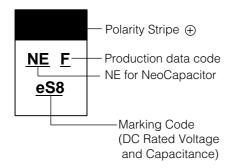
[]: Under development-under specification to be determined.

■ PART NUMBER SYSTEM



TE PSGD0E477M7 -12 R Packing Orientation (R: Cathode on the side of Sproket Hole Tape width (-12: 12 mm) Part number of Bulk Tape and Reel (TE:180mm \$\phi\$ reel) TL PSGD0E477M7 -12 R E Indicate 330mm \$\phi\$ reel

■ MARKINGS



[Rated voltage and capacitance]

UR :Rated Voltage UR 2.5 0E 220 227 [eJ8] 330 337 eN8 eS8 470 477 680 687 eW8

[]: Under development

[Production date code]

YM	Jan.	Feb.	Mar.	Apr.	May	Jun.	Jul.	Aug.	Sep.	Oct.	Nov.	Dec.
2003	а	b	С	d	е	f	g	h	j	k	ı	m
2004	n	р	q	r	S	t	u	٧	W	Х	у	Z
2005	Α	В	С	D	Е	F	G	Н	J	K	L	М
2006	N	Р	Q	R	S	Т	U	V	W	Х	Υ	Z

Note: Production date code will resume beginning in 2007.

■ PERFORMANCE CHARACTERISTICS

Test Conditions: Conform to IEC 60384-1

ITEM			PERFORMANCE		TEST CONDITION
Operating temperature			Derate voltage at 85°C at more		
Rated voltage (V.de	c)		at 85°C		
Derated voltage (V.	.dc)		at 105°C		
Surge voltage (V.do	c)		3.3V		at 85°C
Capacitance			330 μF to 680 μF		
Capacitance tolerar	nce		±20%		at 120 Hz
DC Leakage Currer	nt (L.C)	0.1C •	V(μA) or 3μA, whichever is gr	reater	Voltage: Rated voltage for 5min.
Dissipation Factor			Refer to Standard Ratings		at 120 Hz
Equivalent Series F	Resistance		Refer to Standard Ratings		at 100 kHz
		Capacitance change	DF(%)	L.C	
Surge voltage test		Refer to Standard Ratings	Lower than initial specification	Lower than initial specification	Temperature : 85±2°C Applied voltage : Surge voltage Series resistance : 33 ohm Duration of surge : 30±5 sec Time between surge : 5.5min. Number of cycle : 1000
Characteristic at high and low	-55°C	from 0 to -20%	Lower than initial specification		Step 1: 25±2°C Step 2: -55.3° °C
temperature	+105°C	from 0 to +50%	Lower than 1.5 times initial specification	Lower than 10 times initial specification	Step 3: 25±2°C Step 4: 105.3 °C
Rapid change of temperature		Refer to Standard Ratings	Lower than initial specification	Lower than initial specification	Parts shall be temperature cycled over a temperature range of -55 to +105°C, five times continuously as follow. Step 1: -55.3°C, 30±3min. Step 2: room temp., 10 to 15min. Step 3: 105.3°C, 30±3min. Step 4: room temp, 10 to 15min.
Resistance to Solde heat	ering	Refer to Standard Ratings	Lower than 1.3 times initial specification	Lower than initial specification	Reflow soldering mehod 240°C, 10 sec.Max.
Damp heat		from +30% to -20%	Lower than 1.5 times initial specification	Lower than initial specification	at 40°C at 90 to 95% RH 500 hour
Endurance I		Refer to Standard Ratings	Lower than 1.5 times initial specification	Lower than initial specification	at 85°C at rated voltage 1000 hour
Endurance II		Refer to Standard Ratings Lower than 3 times initial specification Lower than initial specification		at 105°C at Derated voltage 1000 hour	
Failure Rate			at 85°C: rated voltage at 105°C: derated voltage		
Terminal Strength		Visual: There shall be no evidence	Strength: 4.9N Time: 10±0.5sec. (two directions)		
Permissible ripple of	current	Refer to Ratings Table	at 100 kHz		
Other		Conform to IEC60384-1	Conform to IEC60384-1		

Reference : Derated voltage (85 to 105°C)

$$[U_T] = [U_R] - \frac{[U_R] - [U_C]}{20} (T-85)$$

 $\left[U_{T}\right]$: Derated voltage at operating temperature

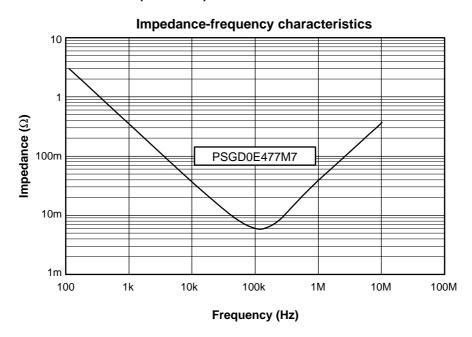
 $[U_R]$: Rated voltage

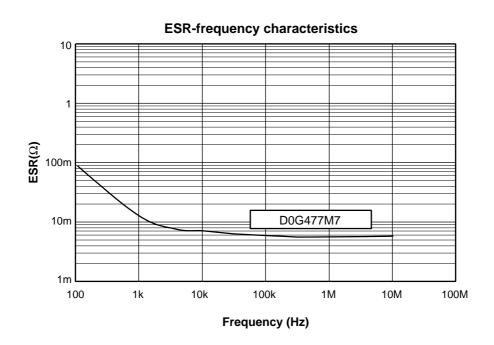
[Uc] : Derated voltage at 105°C T : Ambient temperature

■ STANDARD RATINGS

			_				Permissible	D	F (%)	Capacita	ance
Rated Voltage (V)	Capacitance (μF)	Case Code	Part Number (Bulk)	Leakage Current (μΑ)	DF (%)	ESR (mΩ)	SR Ripple		+125°C	Change 1	Change 2
	330	V	PSGV0E337M9	82.5	10	9	3726	10	15	±20%	±20%
	330	D	PSGD0E337M9	82.5	10	9	4082	10	15	±20%	±20%
	330	D	PSGD0E337M7	82.5	10	7	4629	10	15	±20%	±20%
2.5	470	D	PSGD0E477M9	117.5	10	9	4082	10	15	±20%	±20%
2.5	470	D	PSGD0E477M7	117.5	10	7	4629	10	15	±20%	±20%
	470	D	PSGD0E477M6	117.5	10	6	5000	10	15	±20%	±20%
	680	D	PSGD0E687M9	170	10	9	4082	10	15	±20%	±20%
	680	D	PSGD0E687M7	170	10	7	4629	10	15	±20%	±20%

■ FREQUENCY CHARACTERISTICS (reference)

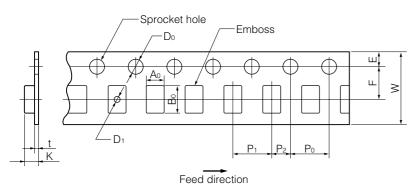




TAPE AND REEL SPECIFICATIONS

■ Plastic Tape Carrier

Unit: mm



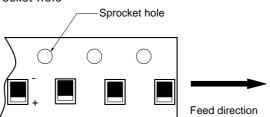
Case Code	A ₀ ± 0.2	B ₀ ± 0.2	K ± 0.2
J	1.0	1.8	1.1
Р	1.4	2.2	1.4
A2 (U)	1.9	3.5	1.4
А	1.9	3.5	1.9
В3	3.2	3.8	1.4
B2 (S)	3.3	3.8	2.1
C2	3.7	6.4	1.7
С	3.7	6.4	3.0
V	4.6	7.7	2.4
D	4.8	7.7	3.3

Unit: mm

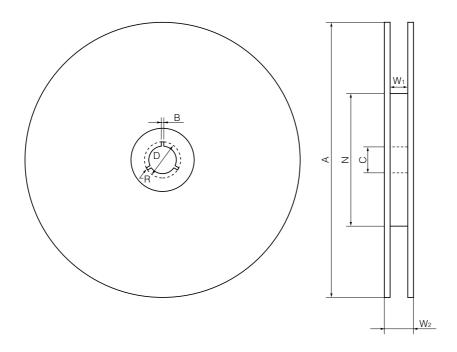
Case Code	W ± 0.3	F ± 0.05	E ± 0.1	P ₁ ± 0.1	P ₂ ± 0.05	P ₀ ± 0.1	D ₀ +0.1	D ₁ min.	t			
J								-				
Р								_				
A2 (U)	8	3.5		4					0.2			
Α	0	3.5		4				,10	0.2			
B3 (W)		1.75		2	4	,4.5	<i>φ</i> 1.0					
B2 (S)			1.75		2	4	φ1.5					
C2									0.2			
С	12		F F	_			0				,15	0.3
V	12	5.5		8				φ1.5	0.4			
D									0.3			

■ Packing Orientation

ex. R:Cathode on the side of Sprocket hole



REEL



Unit: mm

Tape Width	Α	N Min.	C ± 0.5	D	B ± 0.5	W ₁	W₂ Max.	R	
8 mm	φ180 ⁺⁰	.50	.40	,0410 F	0	9.0 ± 1.0	11.4 ± 1.0	4	
12 mm	φ180_3	ϕ 50	<i>φ</i> 13	ϕ 21±0.5	2	13.0 ± 1.0	15.4 ± 1.0	1	
8 mm	/220 L 0	,00	.40	φ13 φ21± 1.0	0		10.0 Max.	14.5 Max.	4
12 mm	ϕ 330 ± 2	ϕ 80	φ13		2	14.0 Max.	18.5 Max.	1 1	

Case Code	ϕ 180 Reel	ϕ 330 Reel
J	4000	_
Р	3000	_
A2 (U)	3000	10000
A	2000	9000
B3 (W)	3000	10000
B2 (S)	2000	5000
C2	1000	4000
V	1000	3000
C, D	500	2500

[Quantity Per Reel]

NOTES ON USING THE SOLID TANTALUM CAPACITORS

About 90% of the failure mode of the solid tantalum capacitor is short-circuit. Please take surplus for the operating condition.

1. Circuit Design

(1) Reliability

The reliability of the solid tantalum capacitor is heavily influenced by environmental conditions such as temperature, humidity, shock, vibration, mechanical stresses, and electric stresses, including applied voltage, current, ripple current, transient current and voltage, and frequency. When using solid tantalum capacitors, therefore, provide enough margin so that the reliability of the capacitors is maintained.

Voltage and temperature are important parameters when estimating the reliability (field failure rate).

The field failure rate of a solid tantalum capacitor can be calculated by the following expression if emphasis is placed only on the voltage and temperature:

$$\lambda = \lambda_0 (V/V_0)^3 \times 2^{(T-T_0)/10}$$

Where

λ: estimated failure rate in actual working condition

temperature: T; voltage: V

λο: failure rate under rated load (See table below.)

temperature: To; voltage: Vo

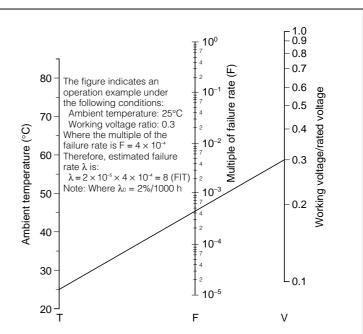
Failure rate level λ_0 of each series

Series	Failure rate level
PS/L	1%/1000 h
E/SV	1%/1000 h
F/SV	1%/1000 h
PS/G	1%/1000 h
SV/Z	1%/1000 h

<Test conditions>

Temperature: 85°C Voltage: rated voltage

Rs: 3 Ω



This figure graphically indicates $(V/V_0)^3 \times 2^{(T-T_0)/10}$ in the expression $\lambda = \lambda_0 \ (V/V_0)^3 \times 2^{(T-T_0)/10}$. By using this figure, the estimated failure rate can be easily calculated.

Connect the desired temperature and voltage ratio with a straight line (from the left most vertical axis in the figure to the right most axis) in the figure. The multiple of the failure rate can be obtained at the intersection of the line drawn and the middle vertical axis in the figure.

Therefore,

 $\lambda = \lambda_0 \times F$

Where

F: multiple of failure rate at given temperature and ratio of working voltage to rated voltage.

2. Ripple Current and Ripple Voltage

If ripple current is applied, heat is generated within capacitor by Joule's heat (power dissipation) and it may affect to the reliability of the capacitor.

(1) Power Dissipation

The actual power dissipated in the capacitor is calculated using the formula1.

$$P = I^2 \times ESR.....Formura1$$

P : Power Dissipation (Watts)
I : Ripple Current (Arms)

ESR : Equivalent Series Resistance (Ω)

(2) Ripple Current

Using P Max from TABLE1, maximum ripple current I (Arms) may be determined as follow:

$$I = \sqrt{P_{Max}/ESR} \times K \times F.....Formura2$$

K: Temperature Derating Factor TABLE2 E/SV, F/SV, SV/Z....TABLE2-1, P/SL, PS/G....TABLE2-2

F : Frequency Derating Factor.....TABLE3

ESR : refer to Ratings

Ripple voltage E is calculated using the formura3.

 $E = Z \times I.....Formura3$

E: Ripple voltage
Z: Impedance at specified frequency

(3) Ripple Voltage

The ripple voltage which may be applied is limited by three criteria:

- (a) The power dissipated in the ESR of the capacitor must not exceed the appropriate value specified in TABLE1.
- (b) The sum of the DC voltage and peak value of the ripple voltage must not exceed the rated voltage.
- (c) The negative peak value of the ripple voltage must not exceed the permissible reverse voltage value specified in the following section, Reverse Voltage.

3. Reverse Voltage

- (1) Because the solid tantalum capacitor is of polar type, do not apply a reverse voltage to it.
- (2) The figure on the right shows the relationship between current and reverse voltage.

TABLE 1 Dissipation Ratings

Case Code	Maximum Power Disspation Watts, 100kHz, at 25°C
J	0.010
Р	0.025
A2	0.060
Α	0.075
B3	0.075
B2	0.085
C2	0.090
С	0.110
V	0.125
D	0.150

TABLE 2-1 E/SV, F/SV, SV/Z Series

Temp.	Temperature Derating Factor K
25°C	1
85°C	0.9
125°C	0.4

TABLE 2-2 P/SL, PS/G Series

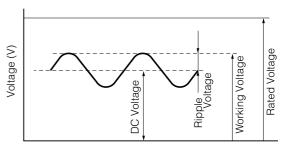
Temp.	Temperature Derating Factor K
25°C	1
85°C	0.9
105°C	0.4

TABLE 3 Frequency Derating Factor F

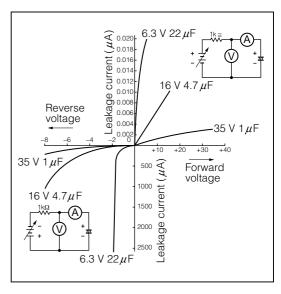
Series	10kHz	100kHz	500kHz	1MHz
I	0.80	1.00	1.15	1.20
П	0.75	1.00	1.10	1.30

I : E/SV, F/SV, SV/Z

Ⅱ: PS/L, PS/G



Time (seconds)



4. Applied Voltage

- (1) For general applications, apply 70% or less of the rated voltage to the capacitor.
- (2) When the capacitor is used in a power line or a low-impedance circuit, keep the applied voltage within 30% (50% max.) of the rated voltage to avoid the adverse influence of inrush current.
- (3) For conductive polymer type, NeoCapacitor, apply 80% or less of the rated voltage to the capacitor.

Recommended Ratio of Operating Voltage to Rated Voltage

Circuit	Manganese dioxide type E/SV, F/SV, SV/Z series	Conductive polymer type (NeoCapacitor) PS/L, PS/G series
high-impedance	70% or less	80% or less
low-impedance	within 30% (50% max)	80% or less

(4) Derated voltage at 85°C or more.

When using a Chip-type capacitor at a temperature of 85° C or higher, calculate reduced voltage U_T from the following expression. Note, however, that the ambient temperature must not exceed the maximum operating temperature.

The rated voltage ratio is as shown in the figure on the right.

$$U_T = U_R - \frac{U_{R} - U_{C}}{T_{max} - 85}$$
 (T-85)

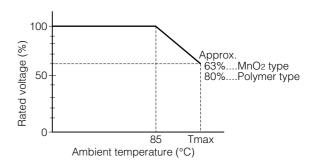
Where

UR: rated voltage (V)

Uc: derated voltage at 125°C T: ambient temperature (°C)

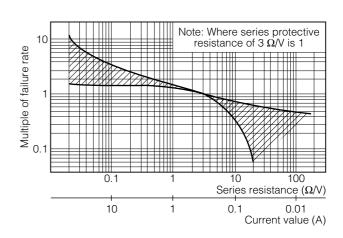
Tmax: Maximum Operating temperature

MnO₂ type E/SV, F/SV, SV/Z......125°C Conductive Polymer type PS/L,PS/G ...105°C



5. Current (Series Resistance)

As shown in the figure on the right, reliability is increased by inserting a series resistance of at least $3\Omega/V$ into circuits where current flow is momentary (switching circuits, charge/discharge circuits, etc). If the capacitor is in a low-impedance circuit, the voltage applied to the capacitor should be less than 1/2 to 1/3 of the DC rated voltage.



6. In the Case of Short-Circuit

- (1) Manganese oxide tantalum capacitor (conventional tantalum capacitor) is heated and may generate fire and be burned depending upon its excess current, time and other factors.
- (2) Conductive polymer tantalum capacitor (NeoCapacitor) is heated and may generate smoke emission depending upon its excess current, time and other factors.

Conductive polymer used for electrolyte is superior in insulanting the damaged portion to manganese oxide (used in conventional tantalum capacitor).

When designing the circuit, provide as much margin as possible to maintain capacitor reliability.

NOTES ON USING THE CHIP TANTALUM CAPACITORS, EXCLUDING NeoCapacitors

1. Mounting

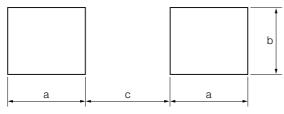
(1) Direct Soldering

Keep the following points in mind when soldering the capacitor by means of jet soldering or dip soldering:

(a) Temporarily fixing resin

Because chip tantalum capacitors are larger and subject to more force than chip multilayer ceramic capacitors or chip resistors, more resin is required to temporarily secure the solid tantalum capacitors. However, if too much resin is used, the resin adhering to the patterns on a printed circuit board may adversely affect the solderability.

(b) Pattern design



(mm)

Case	а	b	С
Р	2.2	1.4	0.7
A2 (U), A	2.9	1.7	1.2
B3 (W), B2 (S)	3.0	2.8	1.6
C2, C	4.1	2.3	2.4
V, D	5.2	2.9	3.7

The above dimensions are for reference only. If the capacitor is to be mounted by this method, and if the pattern is too small, the solderability may be degraded.

(c) Temperature and time

Keep the peak temperature and time within the following values:

Solder temperature 260°C max.

Time 5 seconds max.

Whenever possible, perform preheating (at 150°C max.) for a smooth temperature profile. To maintain reliability, mount the capacitor at low temperature and in a short time.

(d) Component layout

If many types of chip components are mounted on a printed circuit board that is to be soldered by means of jet soldering, solderability may not be uniform over the entire board, depending on the layout and density of the components on the board (also take into consideration generation of flux gas).

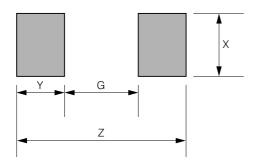
(e) Flux

Use resin-based flux. Do not use flux with strong acidity.

(2) Reflow Soldering

Keep the following points in mind when soldering the capacitor in a soldering oven or with a hot plate:

(a) Pattern design (in accordance with IEC61188)



(mm)

Case	G Max.	Z Min.	X Min.	Y (reference)
J *	0.65	1.65	0.65	0.5
P2*	1.05	2.05	0.80	0.5
A3*	1.65	3.25	1.1	0.8
Р	0.5	2.6	1.2	0.9
A2 (U), A	1.1	3.8	1.5	1.05
B3 (W), B2 (S)	1.4	4.1	2.7	1.35
C2, C	2.9	6.9	2.7	2.0
V, D	4.1	8.2	2.9	2.05

^{*} F/SV Series only (Conform to IEC 61188-5-2)

The above dimensions are recommended. Note that if the pattern is too big, the component may not be mounted in place.

(b) Temperature and time

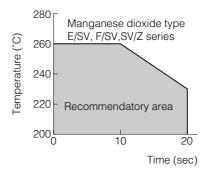
Keep the peak temperature and time within the following values:

Solder temperature...... 260°C max.

Time 10 seconds max.

Whenever possible, perform preheating (at 150°C max.) for a smooth temperature profile. To maintain reliability, mount the capacitor at low temperature and in a short time. The peak temperature and time shown above are applicable when the capacitor is to be soldered in a soldering oven or with a hot plate. When the capacitor is soldered by means of infrared reflow soldering, the internal temperature of the capacitor may rise beyond the surface temperature.

Temperature and Time



(3) Using a Soldering Iron

When soldering the capacitor with a soldering iron, controlling the temperature at the tip of the soldering iron is very difficult. However, it is recommended that the following temperature and time be observed to maintain the reliability of the capacitor:

2. Cleaning

Generally, several organic solvents are used for flux cleaning of an electronic component after soldering. Many cleaning methods, such as immersion cleaning, rinse cleaning, brush cleaning, shower cleaning, vapor cleaning, and ultrasonic cleaning, are available; cleaning methods may be used alone or two or more may be used in combination. The temperature of the organic solvent may vary from room temperature to several 10°C, depending on the desired effect. If cleaning is carried out with emphasis placed only on the cleaning effect, however, the marking on the electronic component cleaned may be erased, the appearance of the component may be damaged, and, in the worst case, the component may be functionally damaged. It is therefore recommended that the R series solid tantalum capacitor be cleaned under the following conditions:

Recommended conditions of flux cleaning

- (1) Cleaning solvent Chlorosen, isopropyl alcohol
- (2) Cleaning method Shower cleaning, rinse cleaning, vapor cleaning
- (3) Cleaning time5 minutes max.

Note. Ultrasonic cleaning

This cleaning method is extremely effective for eliminating dust generated by mechanical processes, but may pose problems depending on the condition. An experiment conducted by NEC TOKIN confirmed that the external terminals of the capacitor were cut when it was cleaned with some ultrasonic cleaning machines. The cause of this phenomenon is metal fatigue of the capacitor terminals due to ultrasonic cleaning. To prevent the terminal from being cut, decreasing the output power of the ultrasonic cleaning machine or shortening the cleaning time may be effective. However, it is difficult to specify the cleaning conditions because there are many factors involved, such as the conversion efficiency of the ultrasonic oscillator, transfer efficiency of the cleaning bath, difference in cleaning effect depending on the location in the cleaning bath, the size and quantity of the printed circuit boards to be cleaned, and the securing states of the components on the boards. It is therefore recommended that ultrasonic cleaning be avoided as much as possible.

If ultrasonic cleaning is essential, make sure through experiments that no abnormalities occur as a result of the cleaning. For further information, consult NEC TOKIN.

3. Other

- (1) Do not subject the capacitor to excessive vibration and shock.
- (2) The solderability of the capacitor may be degraded by humidity. Store the capacitor at room temperature (–5 to +40°C) and humidity (40 to 60% RH).
- (3) Take care that no external force is applied to tape-packaged products (if the packaging material is deformed, the capacitor may not be automatically mounted by a chip mounter).

NOTES ON USING NeoCapacitor

1. Permissible Ripple Current

Permissible ripple current shall be derated as follows:

(1) Temperature Change

25°C: Rating value

85°C: 0.9 times rating value 105°C: 0.4 times rating value

(2) Switching Frequency

10 kHz: 0.75 times rating value

100 kHz: rating value

500 kHz: 1.1 times rating value 1 MHz: 1.3 times rating value

2. Mounting

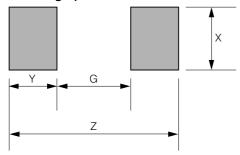
This capacitor is designed to be surface mounted by means of reflow soldering.

(The conditions under which the capacitor should be soldered with a soldering iron are explained in (2) Using a Soldering Iron. Because the capacitor is not designed to be soldered by means of laser beam soldering, VPS, or flow soldering, the conditions for these soldering methods are not explained in this document.

(1) Reflow Soldering

Keep the following points in mind when soldering the capacitor in a soldering oven with a hot plate:

(a) Pattern design (in accordance with IEC61188)



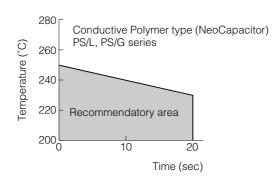
(mm)

Case	G Max.	Z Min.	X Min.	Y (reference)
J	0.7	2.5	1.0	0.9
Р	0.5	2.6	1.2	1.05
A2 (U), A	1.1	3.8	1.5	1.35
B3 (W), B2 (S)	1.4	4.1	2.7	1.35
C2, C	2.9	6.9	2.7	2.0
V, D	4.1	8.2	2.9	2.05

The above dimensions are recommended. Note that if the pattern is too big, the component may not be mounted in place.

(b) Temperature and time

Keep the peak temperature and time within the following recommended conditions.



Whenever possible, perform preheating (at 150°C max.) for a smooth temperature profile. To maintain reliability, mount the capacitor at low temperature and in a short time. The peak temperature and time shown above are applicable when the capacitor is to be soldered in a soldering oven or with a hot plate. When the capacitor is soldered by means of infrared reflow soldering, the internal temperature of the capacitor may rise beyond the surface temperature.

(2) Using a Soldering Iron

When soldering the capacitor with a soldering iron, controlling the temperature at the tip of the soldering iron is very difficult. However, it is recommended that the following temperature and time be observed to maintain the reliability of the capacitor:

Iron temperature ... 350°C max.
Time 3 seconds max.
Iron power 30 W max.

3. Cleaning

Generally, several organic solvents are used for flux cleaning of an electronic component after soldering. Many cleaning methods, such as immersion cleaning, rinse cleaning, brush cleaning, shower cleaning, vapor cleaning, and ultrasonic cleaning, are available, whith may be used alone or in combination. The temperature of the organic solvent may vary from room temperature to several 10°C, depending on the desired effect. If cleaning is carried out with emphasis placed only on the cleaning effect, however, the marking on the electronic component cleaned may be erased, the appearance of the component may be damaged, and, in the worst case, the component may be functionally damaged. It is therefore recommended that the NeoCapacitor be cleaned under the following conditions:

[Recommended conditions of flux cleaning]

- (1) Cleaning solvent Isopropyl alcohol
- (2) Cleaning method Shower cleaning, rinse cleaning, vapor cleaning
- (3) Cleaning time 5 minutes max.

Note: Ultrasonic cleaning

This cleaning method is extremely effective for eliminating dust generated by mechanical processes, but may pose problems, depending on the condition. An experiment conducted by NEC TOKIN confirmed that the external terminals of the capacitor were cut when it was cleaned with some ultrasonic cleaning machines. The cause of this phenomenon is metal fatigue of the capacitor terminals due to ultrasonic cleaning. To prevent the terminal from being cut, decreasing the output power of the ultrasonic cleaning machine or decreasing the cleaning time may be effective. However, it is difficult to specify safe cleaning conditions because there are many factors involved, such as the conversion efficiency of the ultrasonic oscillator, transfer efficiency of the cleaning bath, difference in cleaning effect depending on the location in the cleaning bath, the size and quantity of the printed circuit boards to be cleaned, and the securing states of the components on the boards. It is therefore recommended that ultrasonic cleaning be avoided as much as possible.

If ultrasonic cleaning is essential, make sure through experiments that no abnormalities occur as a result of the cleaning. For further information, contact NEC TOKIN.

NEC/TOKIN

4. Derating

Apply appropriate voltage to the capacitors according to the failure rate estimation. It is recommended that the applied voltage be less than 80% of the rated voltage.

5. Other

- (1) Do not subject the capacitor to excessive vibration and shock.
- (2) The solderability of the capacitor may be degraded by humidity. Store the capacitor at room temperature (–5 to +40°C) and humidity (40 to 60% RH).
- (3) Take care that no external force is applied to tape-packaged products (if the packaging material is deformed, the capacitor may not be automatically mounted by automatic insertion equipment).

The information in this document is based on documents issued in Jan. 2005 at the latest. The information is subject to change without notice. For actual design-in, refer to the latest of data sheets, etc., for the most up-to-date specifications of the device.

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